



# PHOTONICS BASED TERAHERTZ SOURCES

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IMEP-LAHC – UMR CNRS 5130

Séminaire de Confinement Avril 2020

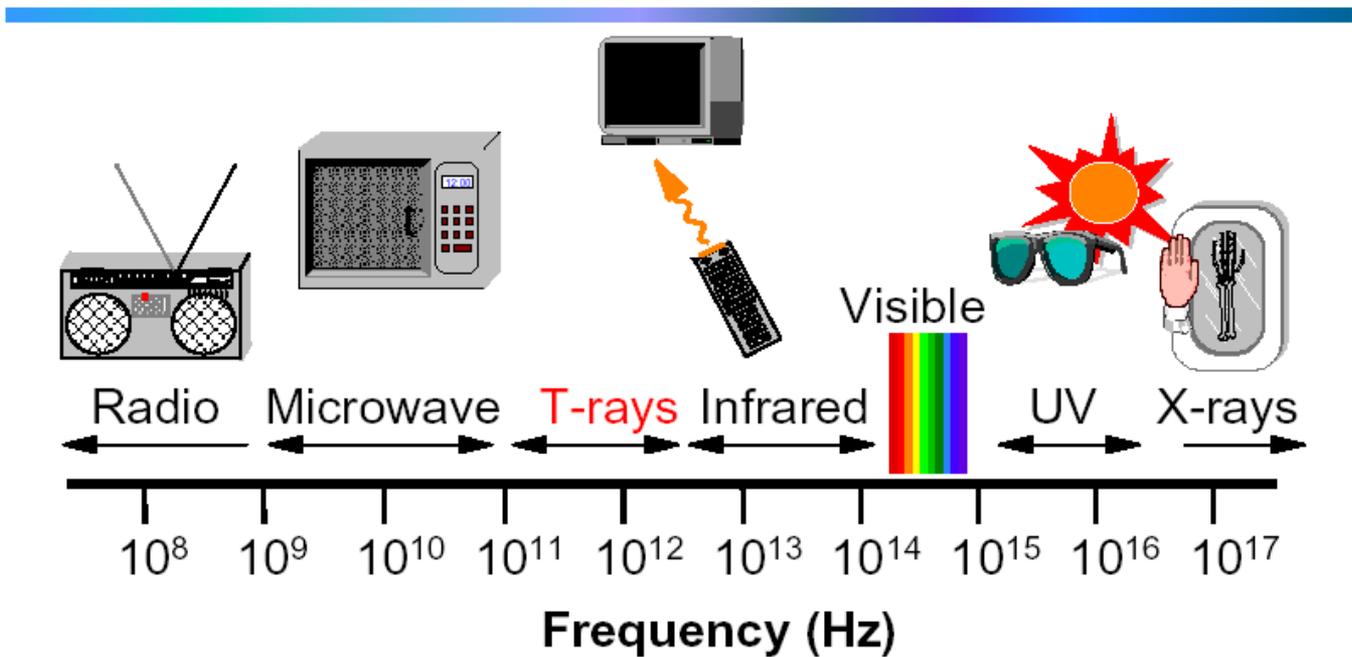


# Outline of the talk

1. Introduction
2. Direct emission of THz waves
3. Down-conversion of photonic sources
4. Conclusion

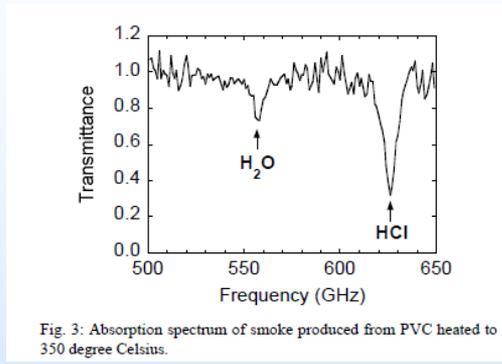
# TeraHertz Spectrum

What is terahertz radiation?

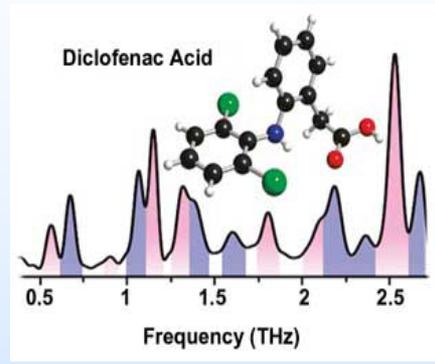


$\nu = 1 \text{ THz}$   $\longrightarrow$   $\lambda = 300 \mu\text{m}$   
 $\longrightarrow$   $h\nu = 33 \text{ cm}^{-1}$  or  $4.1 \text{ meV}$   
 $\longrightarrow$   $T = 48 \text{ K}$

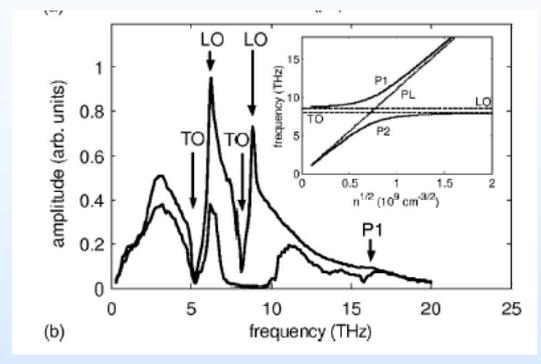
# Different type of applications



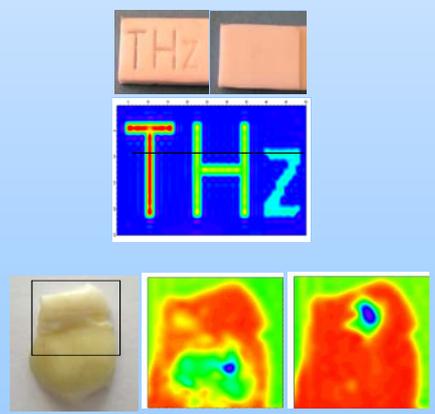
High resolut<sup>o</sup> spectroscopy



Broadband spectroscopy



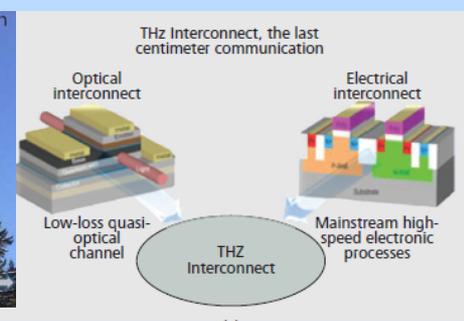
Ultra Broadband spectroscopy



Vision and Non destructive Control



Wireless Telecommunications

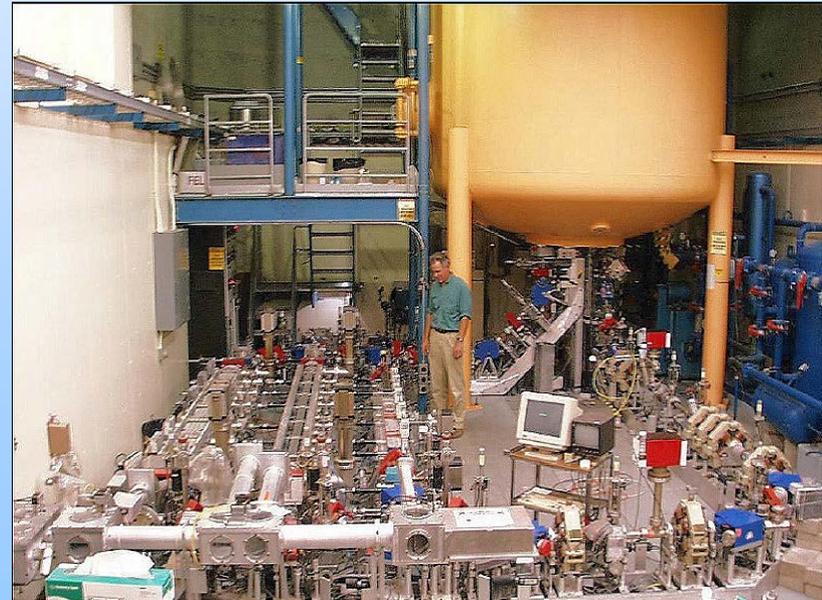


# Which sources for THz studies ?



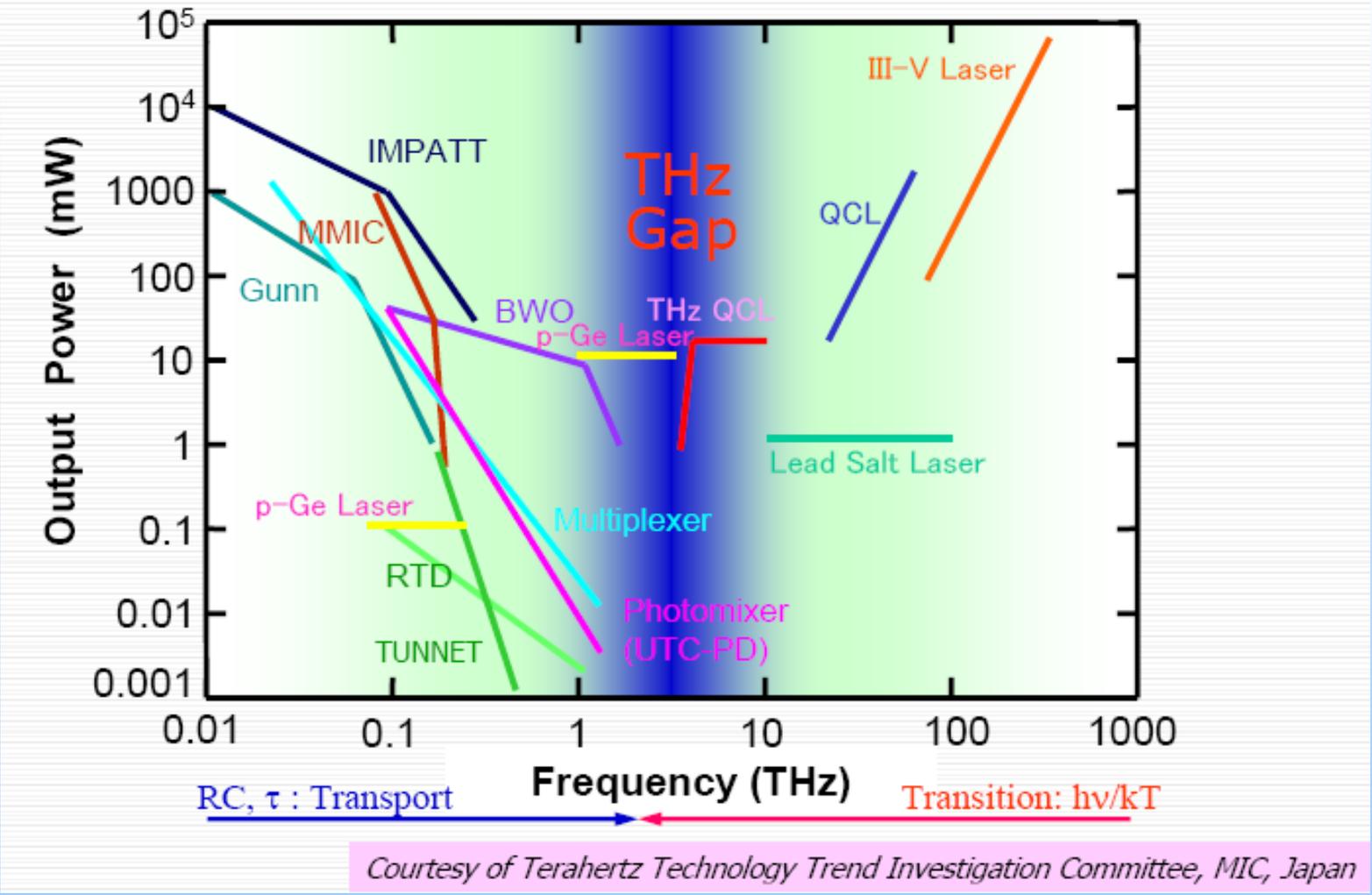
Tape\* ?

Or Free Electron laser ?



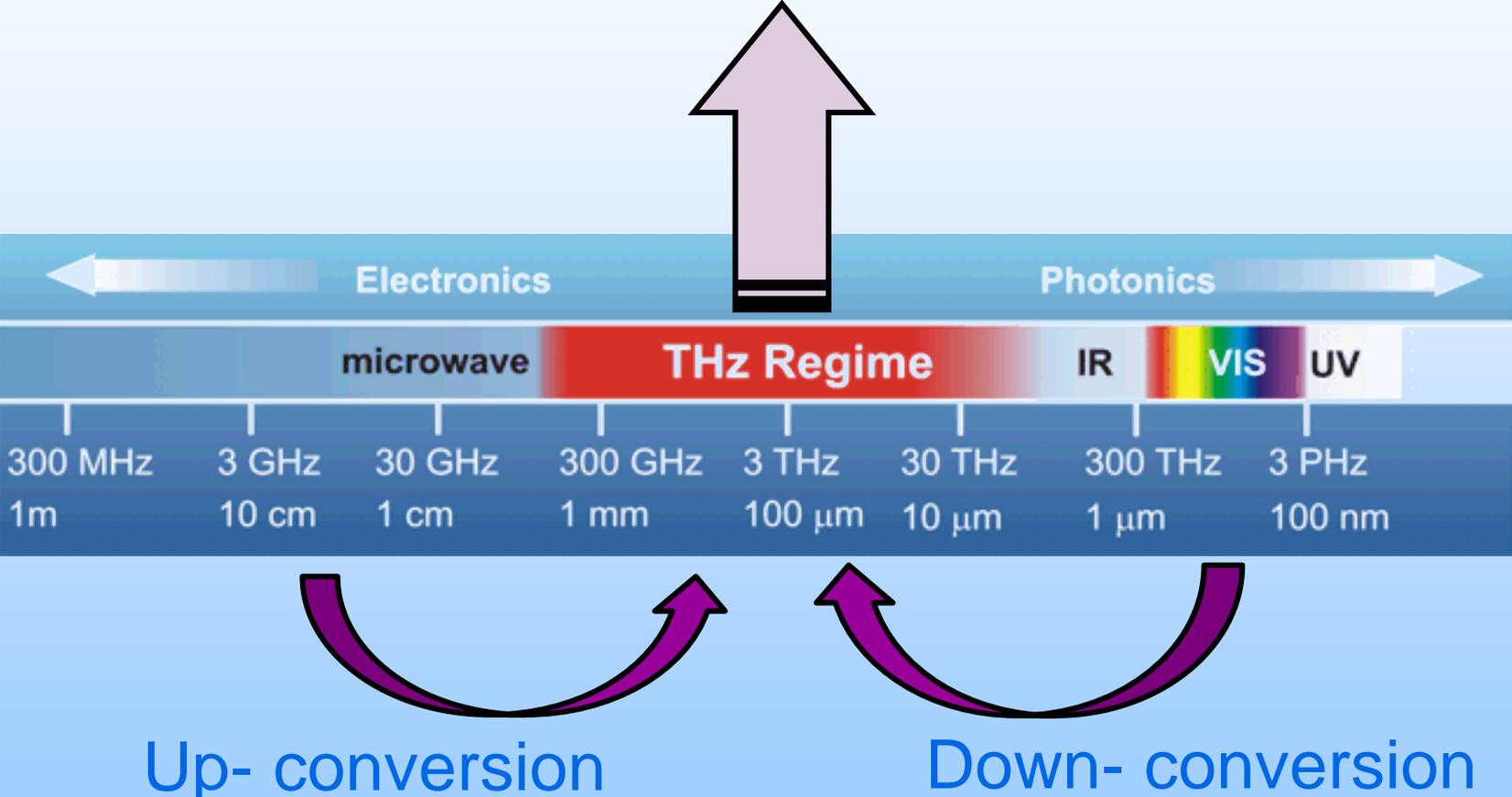
\*Tribocharging effect : Opt. Lett. 34, 2195–2197; 2009

# Which sources ? The THz “Gap”



# Different ways of generating THz

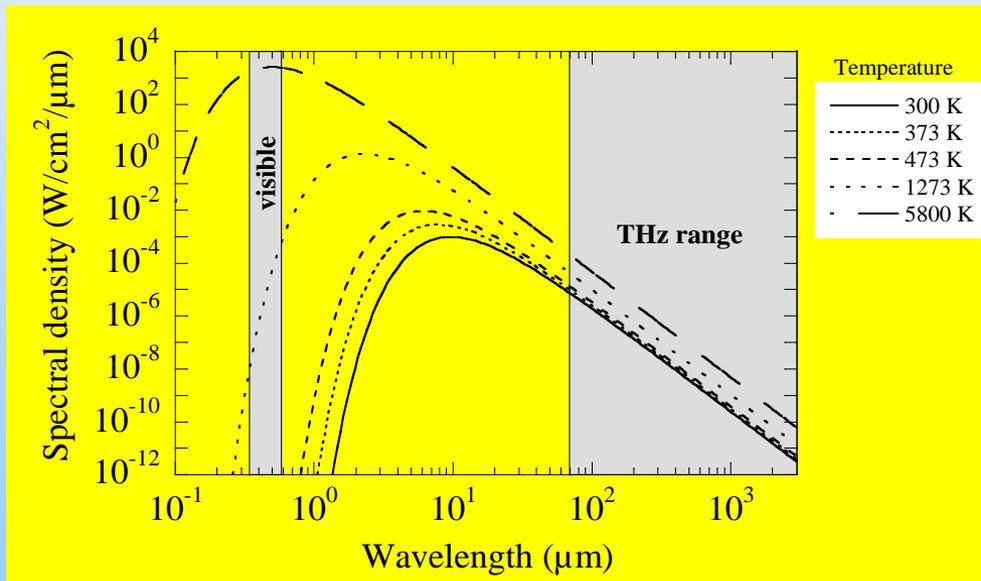
## Direct THz Emission



# Direct emission of THz signal

## ■ Blackbody radiation :

incoherent, broadband, very weak power ( $\sim$  nW)

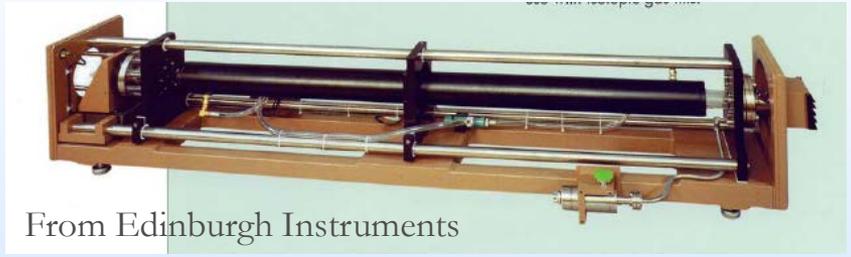


- Commonly used in FTIR spectrometer



# THz lasers

## ■ Molecular lasers



From Edinburgh Instruments

« Not very stable », « powerful »

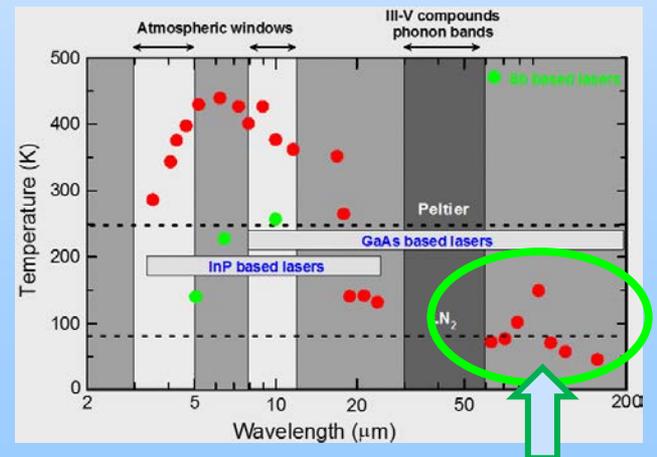
FIR100 FAR INFRARED OUTPUT SPECIFICATION			
$\lambda$ ( $\mu\text{m}$ )	FIR MOLECULE	CO <sub>2</sub> PUMP LINE	POWER
96.5	CH <sub>3</sub> OH	9R10	>60mW
118.8	CH <sub>3</sub> OH	9P36	>150 mW
184.3	CH <sub>2</sub> F <sub>2</sub>	9R32	>150mW
432.6	HCOOH	9R20	>30mW
513.0	HCOOH	9R28	>10mW

## ■ Quantum cascade lasers



**Easy QCL: Turnkey Terahertz Source**  
 The **Easy QCL** is a terahertz QCL system capable of producing peak power levels of >20 mW and average power levels of >1 mW at frequencies between 1.8 and 5 THz. The system features user replaceable QCL modules for maximum experimental flexibility, in a compact package that minimizes optical table use.

1 mW average power in the 1.8 – 5 THz range  
 20 mW pulsed power  
 20 000 \$ (QCL) + 100 000 \$ (cryo-cooler)



**THz QCL's (f > 3 THz)**

# Down Conversion of Photonic sources

- Down-conversion of two cw laser frequency

  - Dedicated dual wavelength lasers

  - THz cw generation in ultrafast photodetectors

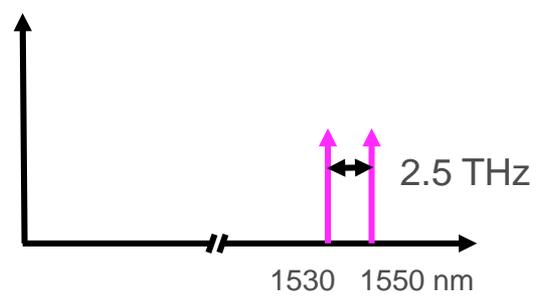
- Down-conversion of fs laser pulses

  - THz pulse generation in ultrafast photoswitches

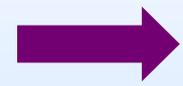
  - THz pulse generation in non-linear crystals

# From IR down to THz: case of CW regime

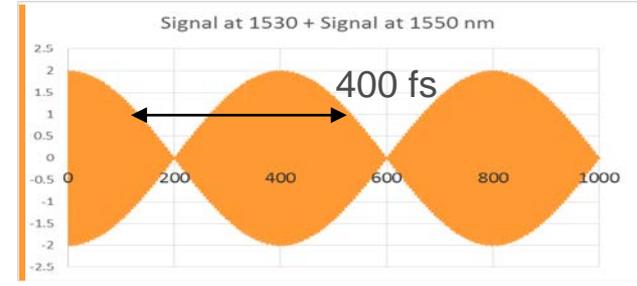
2 laser lines



FFT



Optical beating



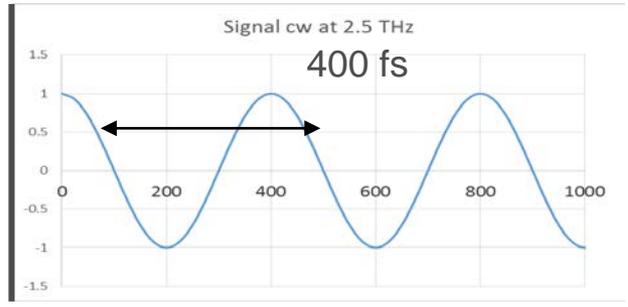
Envelope detection



TERAHERTZ line

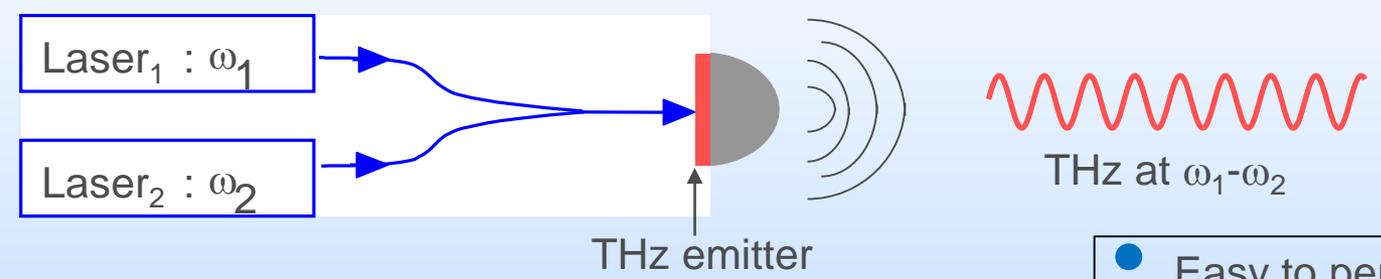


FFT<sup>-1</sup>



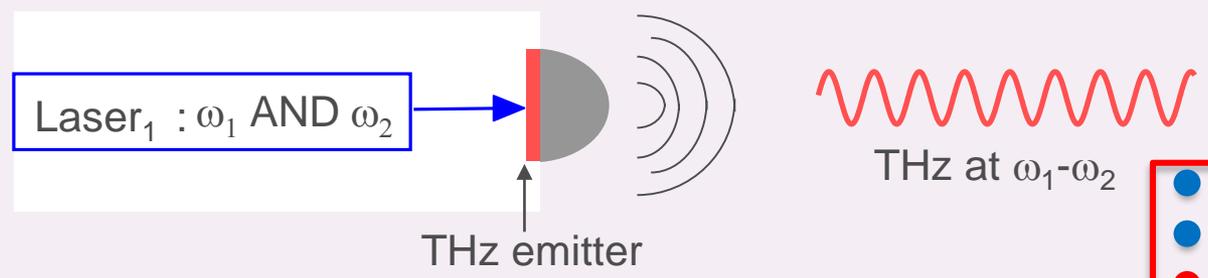
# Dedicated dual-wavelength lasers for THz CW generation

- Classical cw THz generation by optical beating of two lasers



- Easy to perform
- Tunable
- Reduced frequency stability

- CW THz generation using dual-wavelength laser



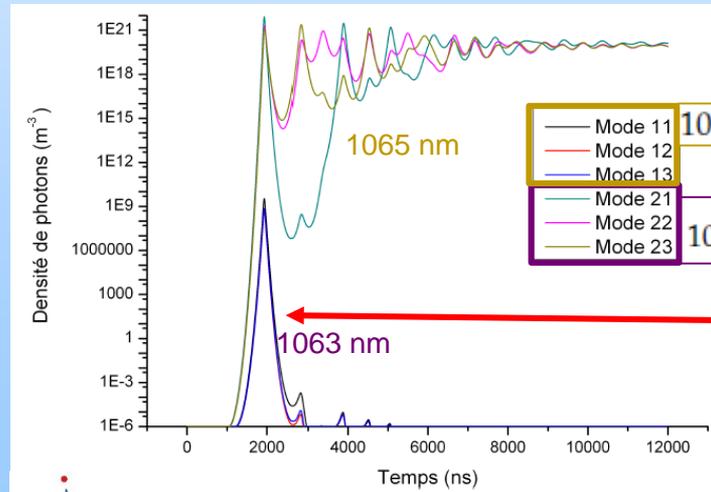
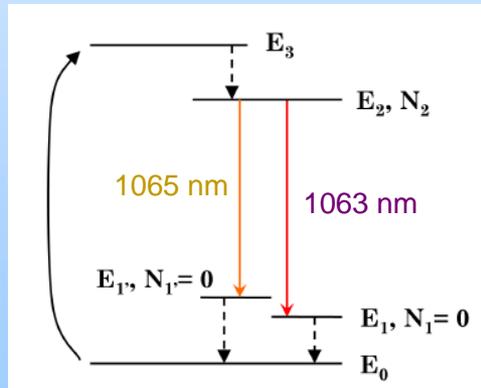
- Stable
- Compact
- Tunable ?

# Dual-wavelength micro-lasers for THz generation

- Neodyme based laser offer high gain and large panel of available crystals
- CW or Q:switch regime
- **Central wavelength has to match THz emitter technology**
- **Gain competition in between different laser modes**



Example : **Dual wavelength operation in Nd:GdVO<sub>4</sub>**



1065 nm :  $\sigma_2 = 2,1 \cdot 10^{-23} \text{ m}^2$

1063 nm :  $\sigma_1 = 1,8 \cdot 10^{-23} \text{ m}^2$

The modes lasing at the less efficiently pumped wavelength are « killed »



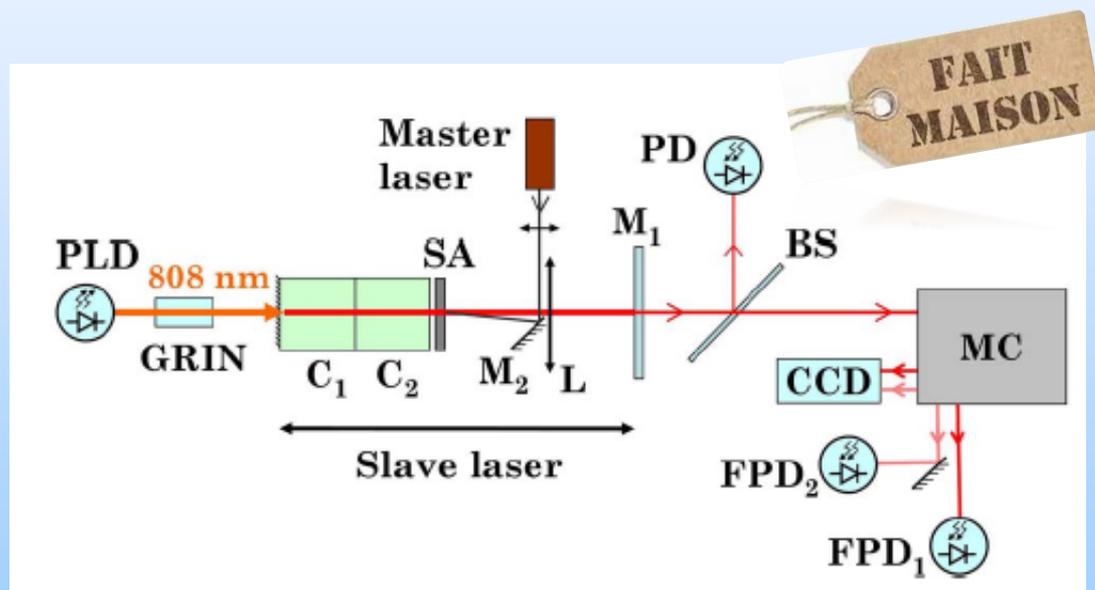
# 2-color micro-laser externally triggered

- Beating in between two lasing transitions of two different crystal placed in 1 cavity

July 15, 2012 / Vol. 37, No. 14 / OPTICS LETTERS 2817

## Simultaneous passively Q-switched dual-wavelength solid-state laser working at 1065 and 1066 nm

Florent Pallas,<sup>1</sup> Emilie Herault,<sup>2</sup> Jean-Francois Roux,<sup>2</sup> Antoine Kevorkian,<sup>3</sup> Jean-Louis Coutaz,<sup>2</sup> and Guy Vitrant<sup>1,\*</sup>



LC1 : Nd:GdVO<sub>4</sub>

LC2 : Nd:YVO<sub>4</sub>

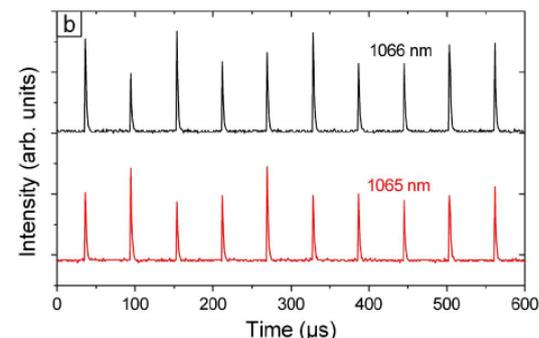
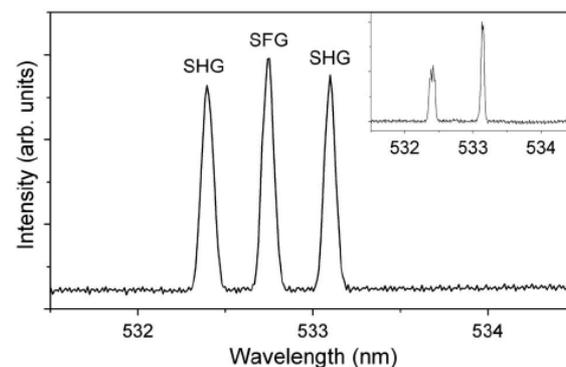


Fig. 2. (Color online) Typical pulse train: a, without external triggering; b, with optimal triggering.



30 ns pulse duration

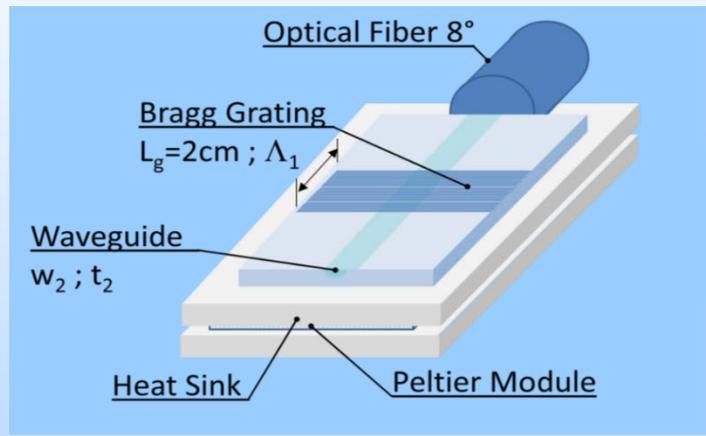
70 W peak power

100 % synchronizat°

# Integrated lasers on glass for THz generation

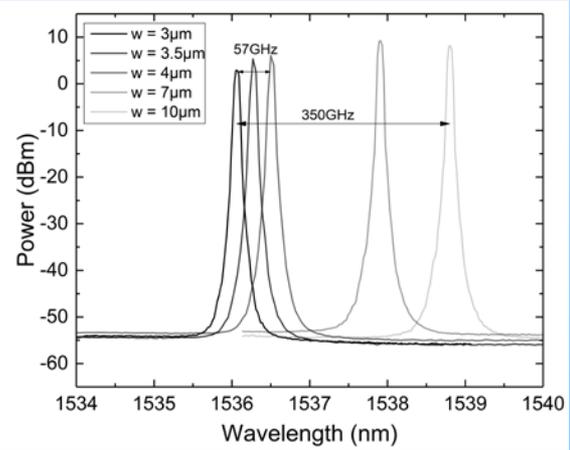
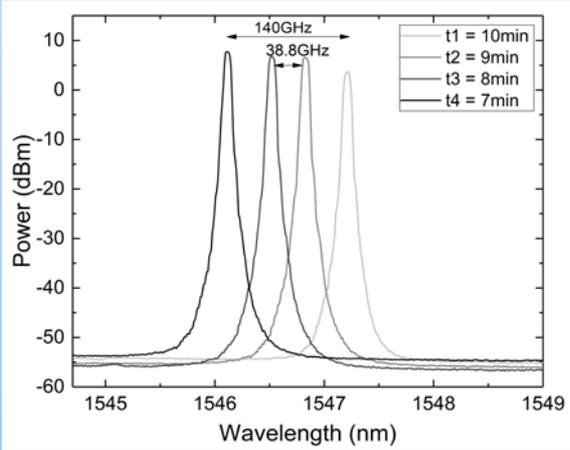
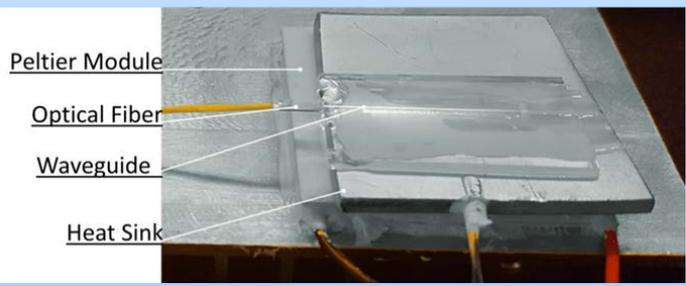
- Verre IOG1 co-dopé Er-Yb
- Cavité DFB

- Guide monomode  $w$
- Pompage à  $\sim 980\text{nm}$



**Contrôle de la longueur d'onde émise**

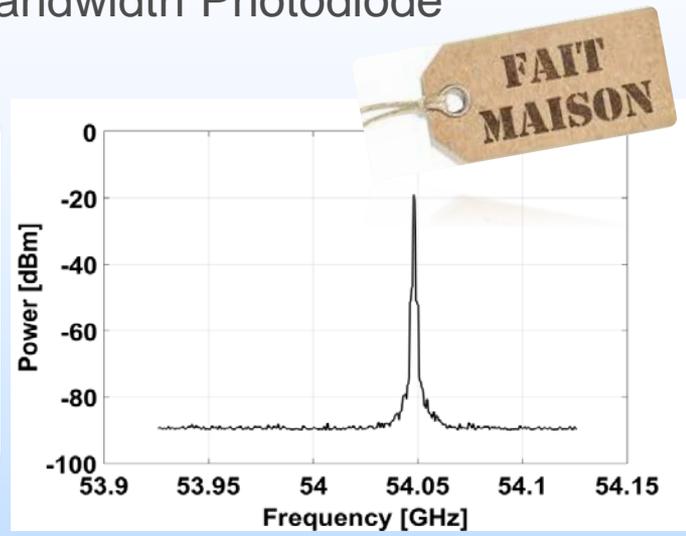
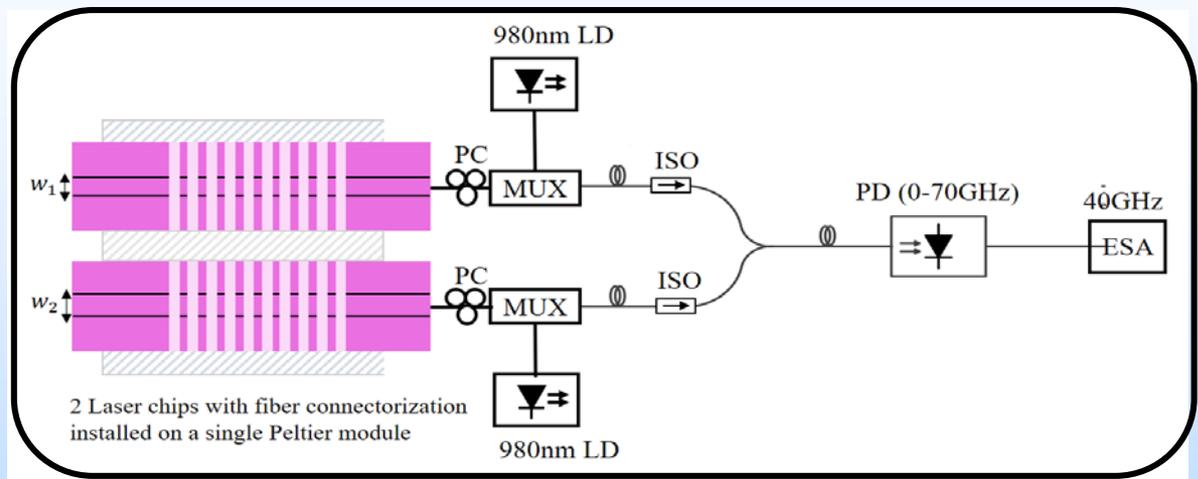
- Cavité optique                      réseau
- Largeur du guide                    masque
- Profondeur du guide                temps d'échange
- Température                           utilisation



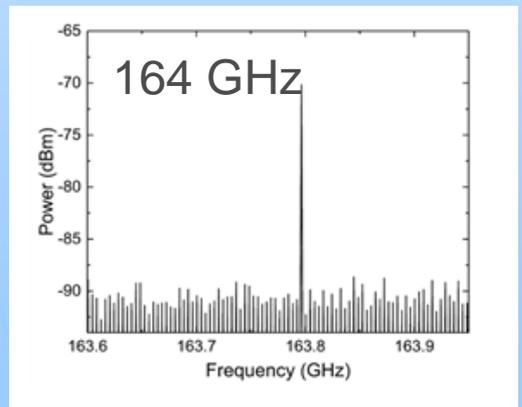
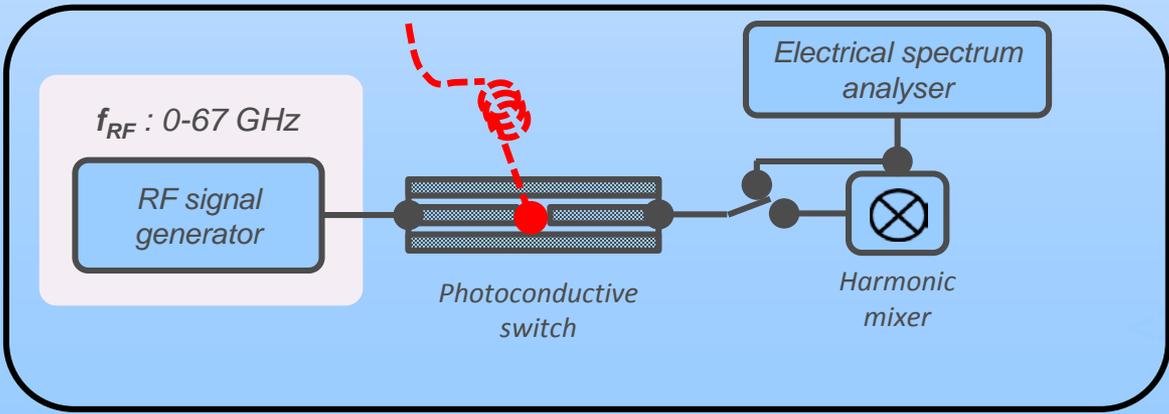
# Integrated lasers : RF generation and detection



## Photodetection of a sub-THz laser beat using a High Bandwidth Photodiode

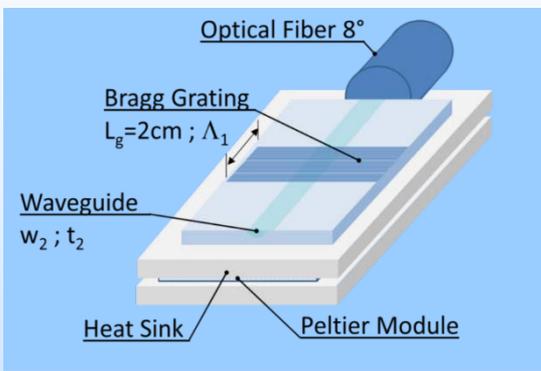


## Heterodyne detection set-up for above 70 GHz generation and detection

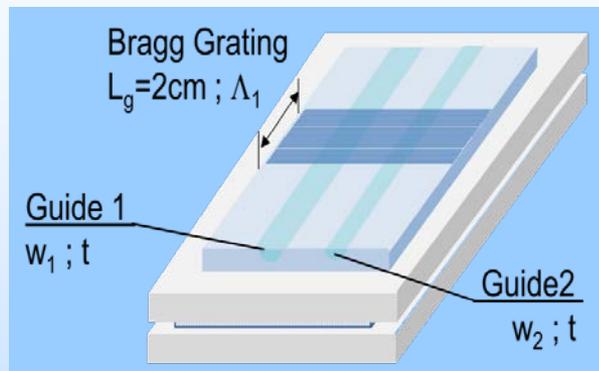


# Integrated lasers : basic and advanced solutions

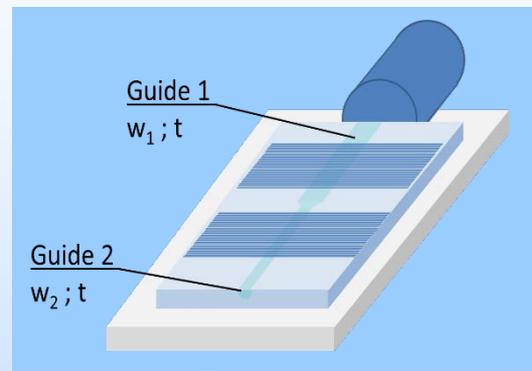
Beating of 2 lasers



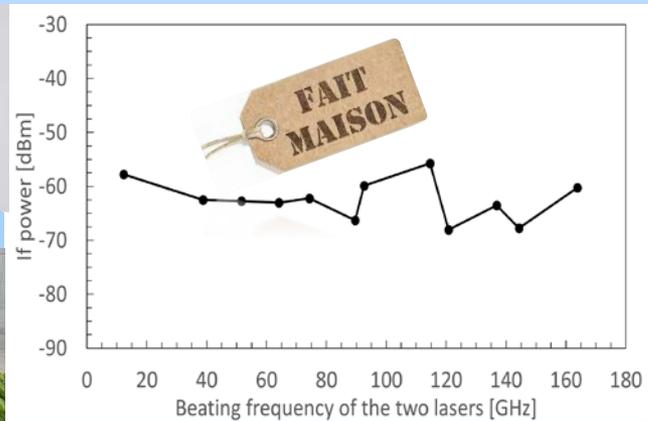
Co-integrated lasers



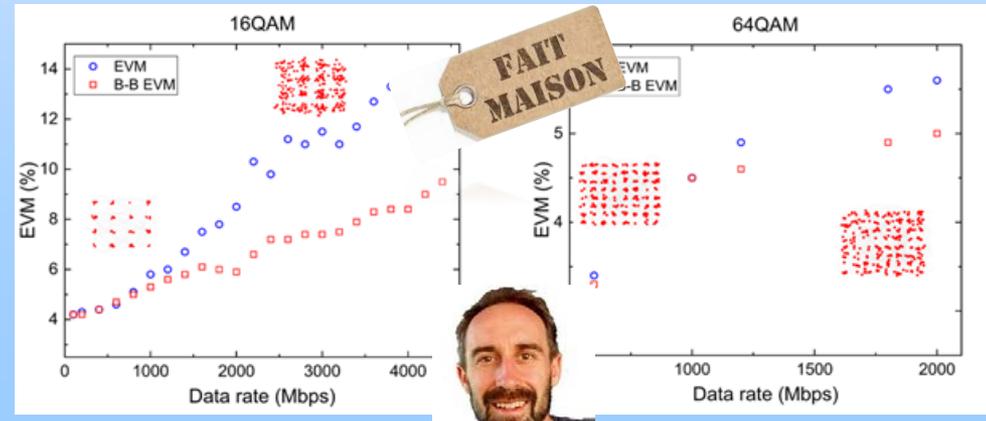
Dual wavelength lasers



Up to 170 GHz detected beating

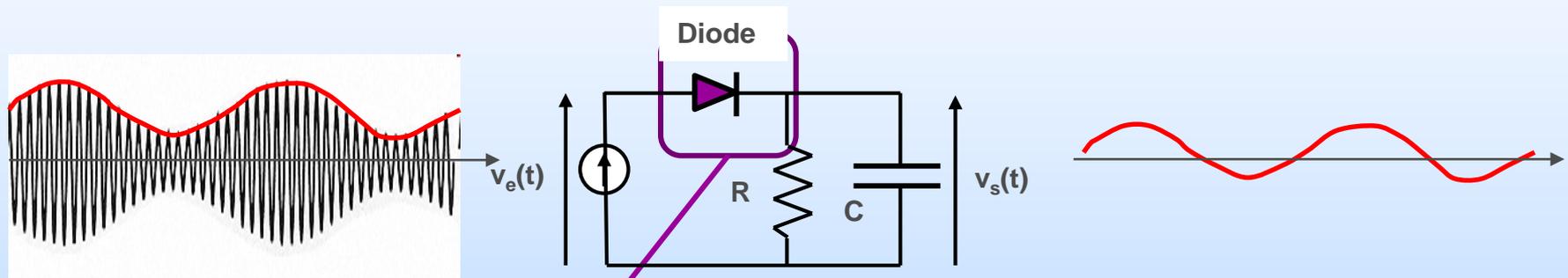


Demonstration of Multi-Gigabits RoF solutions



# Optical mixers for Down Conversion of Photonic sources

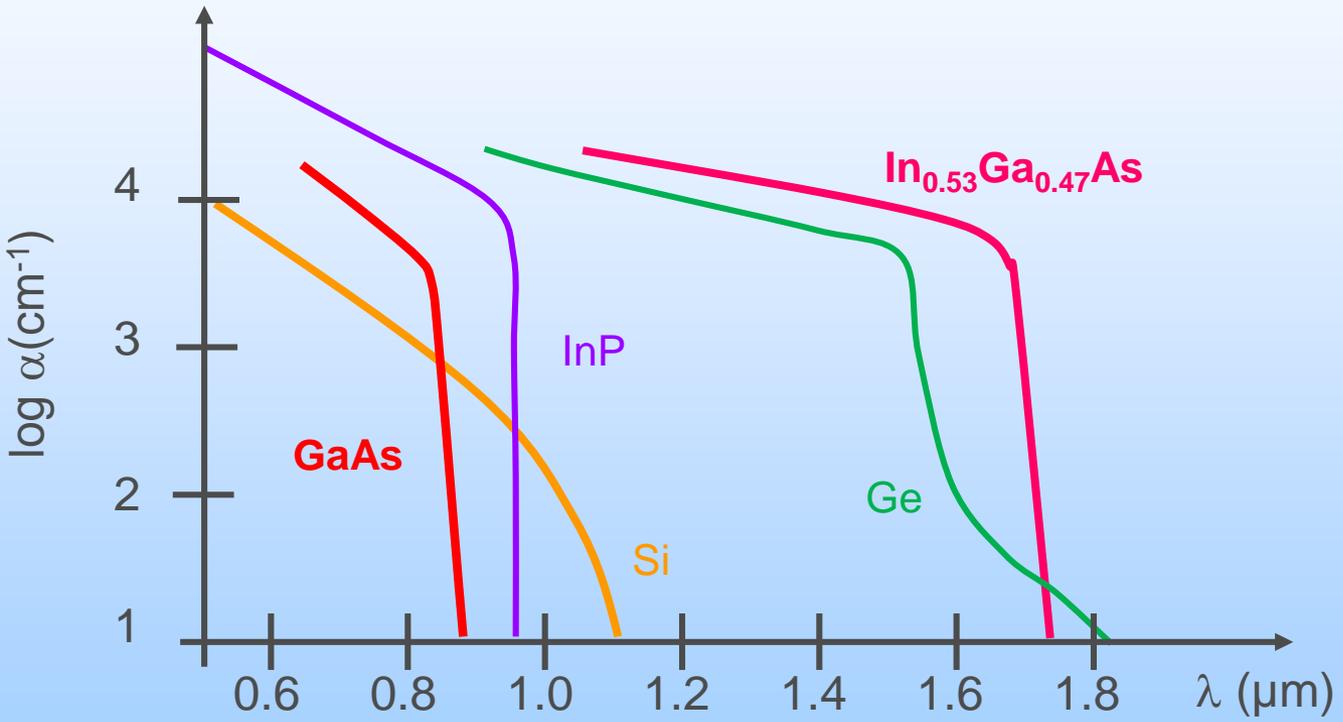
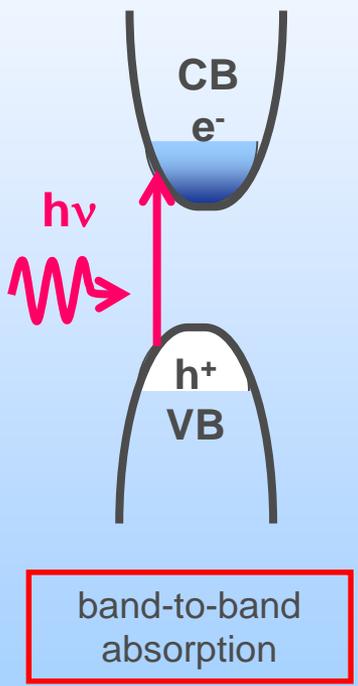
- Amplitude demodulation in Radio = Enveloppe detection = frequency downconversion



Which nonlinear element sensitive to optical frequencies ?

Resonant nonlinear phenomena	Non-resonant nonlinear phenomena
Electron/ holes pair generation by absorption in an opaque media	Difference frequency generation in a transparent nonlinear media

# Optical absorption in semiconductors reminder

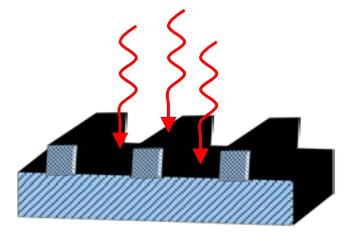


Visible Range GaAs absorbs 10 times more than Si  
NIR Range : Only InGaAs or Ge can be used

# Different kind of photodetectors

## Photoswitches

-  Absorption Layer
-  Contact layers



Metal electrodes  
Intrinsic GaAs

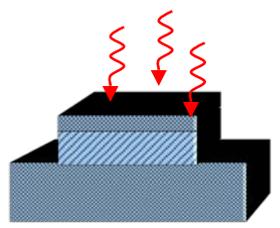
### Features

Simple, Planar,  
**No internal Field**  
Lifetime or transit time limited  
Low Capacitance  
Low Quantum Efficiency

## Photodiodes

-  Absorption Layer
-  Contact layers

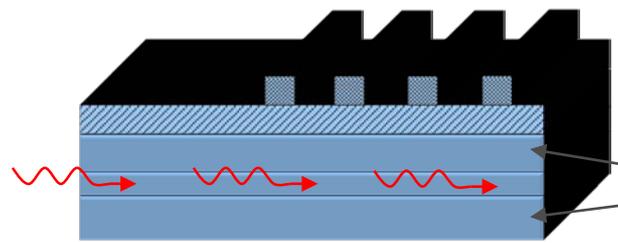
*PIN*



P+ Contact  
Intrinsic Absorption  
N+ Contact

Trade-off Between  
Quantum efficiency  
and Speed

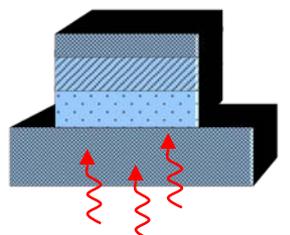
*Waveguide*



Absorption Layer  
Guide Layers

High efficiency  
High speed  
Difficult to couple into

*Uni Travelling Carrier*

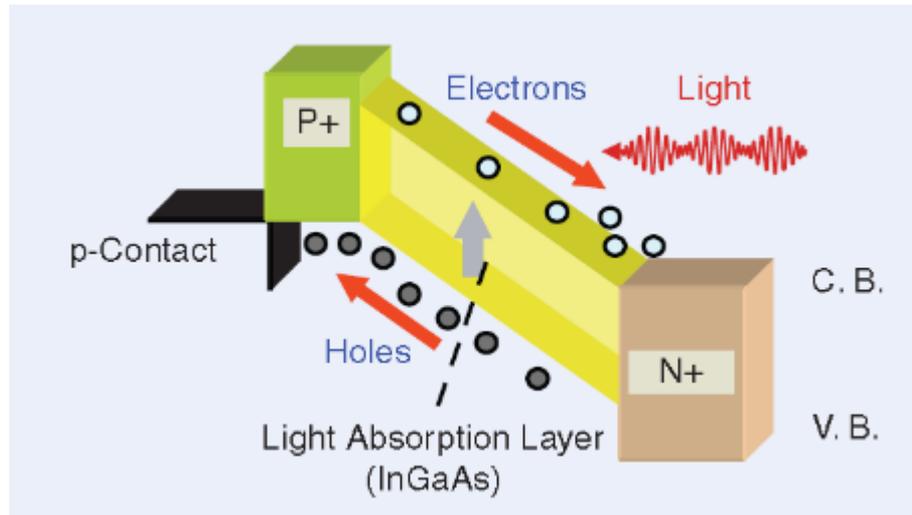


P+ Contact  
P Absorption layer  
Transparent intrinsic layer  
N+ Contact

Very High Speed  
High Efficiency

# High-Frequency detection at 1.55 $\mu\text{m}$

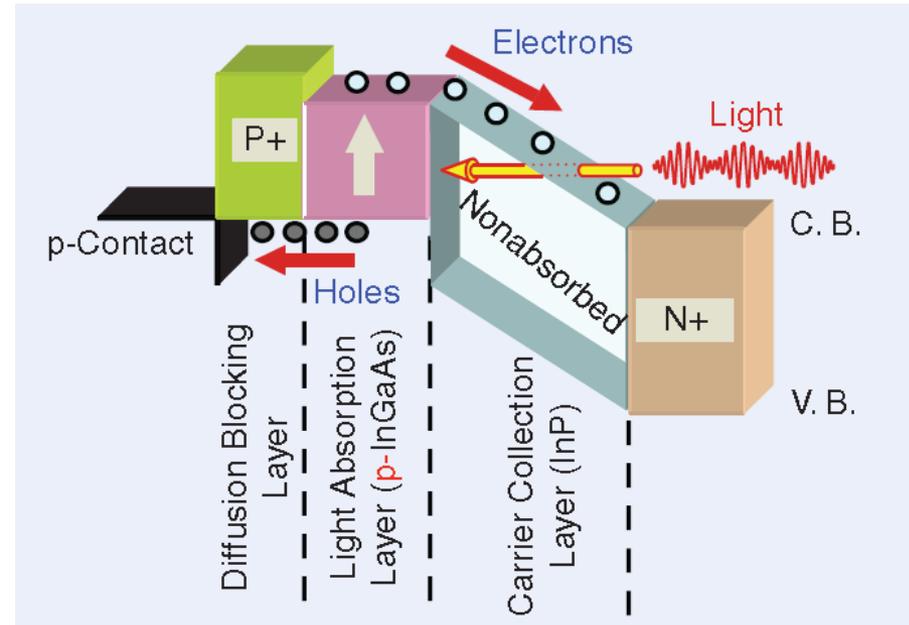
## pin-PD



Holes are slow !

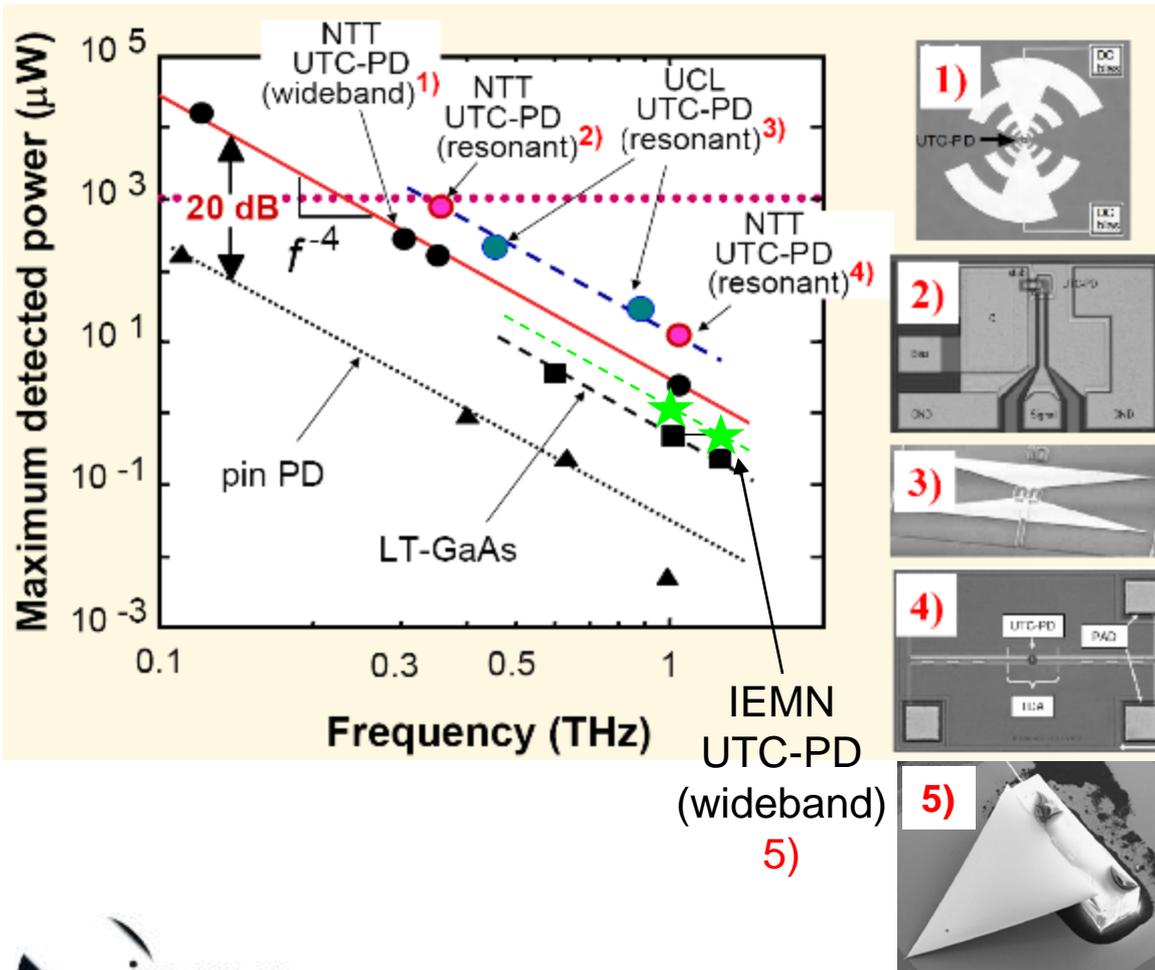
- Low frequency cut-off
- Saturation

## Uni-Travelling Carrier-PD



Proposed at NTT in 1996  
(T. Ishibashi *et al.*)

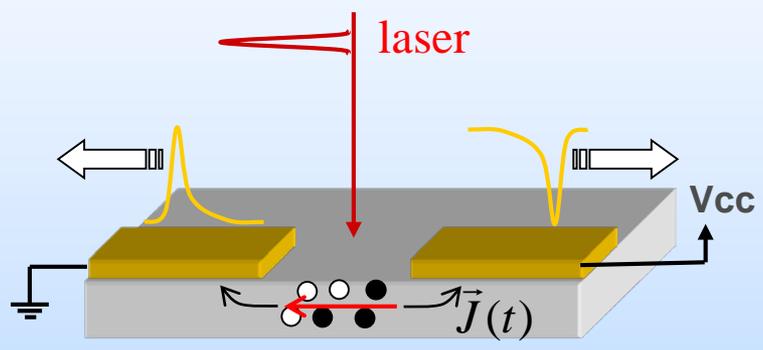
# UTC-PD: State of the art



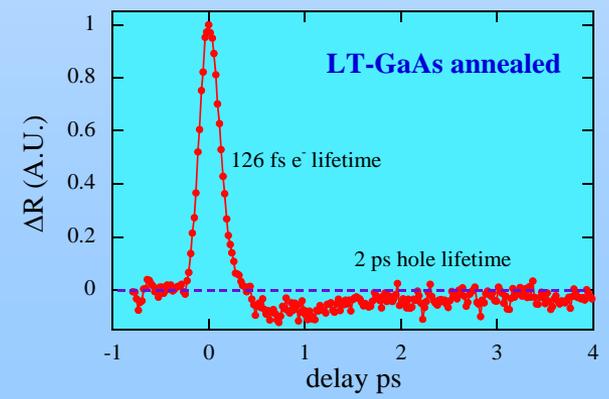
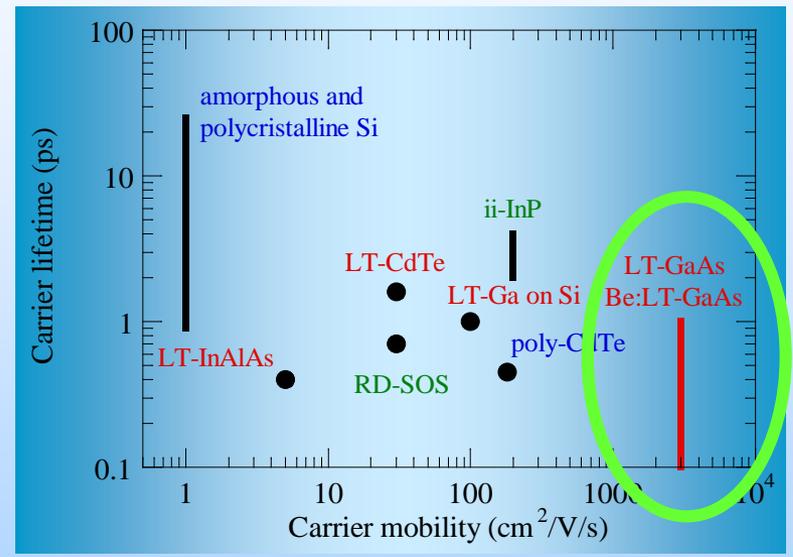
- Wideband antenna  
 $\approx 1\text{-}2 \mu\text{W} @ 1 \text{ THz}$
- Resonant antenna  
 $\approx 10\text{-}20 \mu\text{W} @ 1 \text{ THz}$   
 $\approx 500 \mu\text{W} @ 350 \text{ GHz}$

# Principle of Ultrafast photoswitches

- Optically controlled resistor with **carrier lifetime limited response** :



- No internal Field
- High Bandwidth due to ultrashort carrier Lifetime limited**
- Low Capacitance
- Low Quantum Efficiency

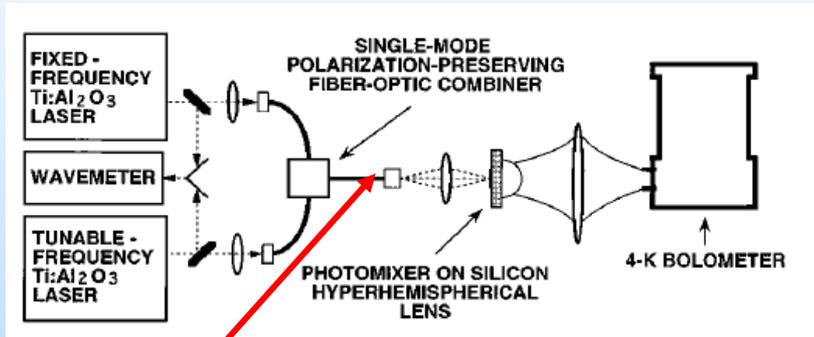


# CW photoconducting emission with interdigitated LTG-GaAs structures

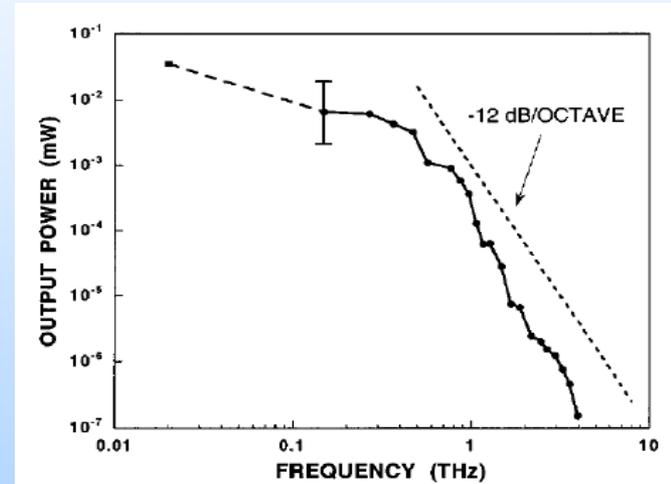
## Photomixing up to 3.8 THz in low-temperature-grown GaAs

E. R. Brown, K. A. McIntosh, K. B. Nichols, and C. L. Dennis

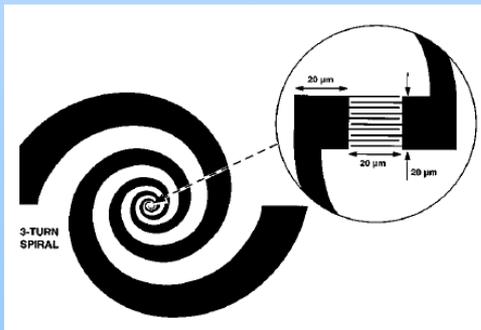
Lincoln Laboratory, Massachusetts Institute of Technology, Lexington, Massachusetts 02173-9108



Beating of 2 Ti:Sa CW lasers



Broadband spiral antenna



Appl. Phys. Lett., vol. 66, p. 285 (1995)

$$P_{rad} \propto \frac{P_1 P_2}{(1 + (\omega R_L C)^2)(1 + (\omega \tau_c)^2)}$$

$$\tau_c = 270 \text{ fs}$$

$$R_L C = 210 \text{ fs}$$

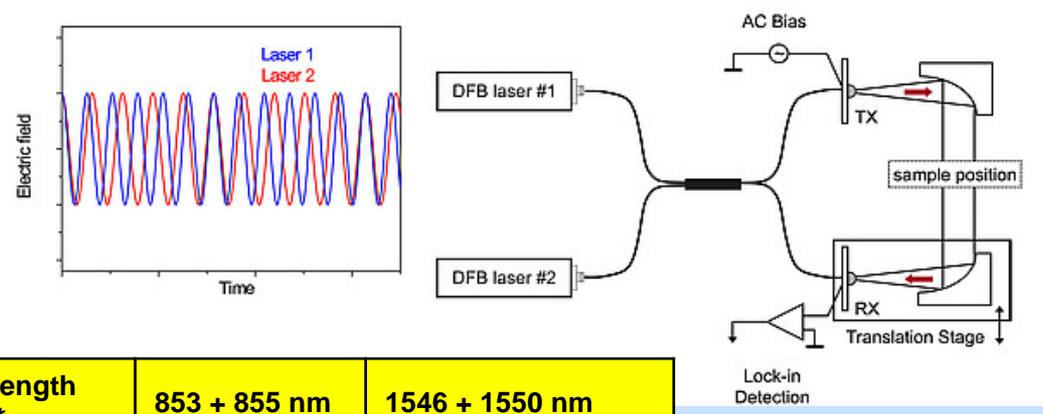
$$P_{Rad} = 0.01 \text{ mW}$$

$$P_{opt} = 100 \text{ mW}$$

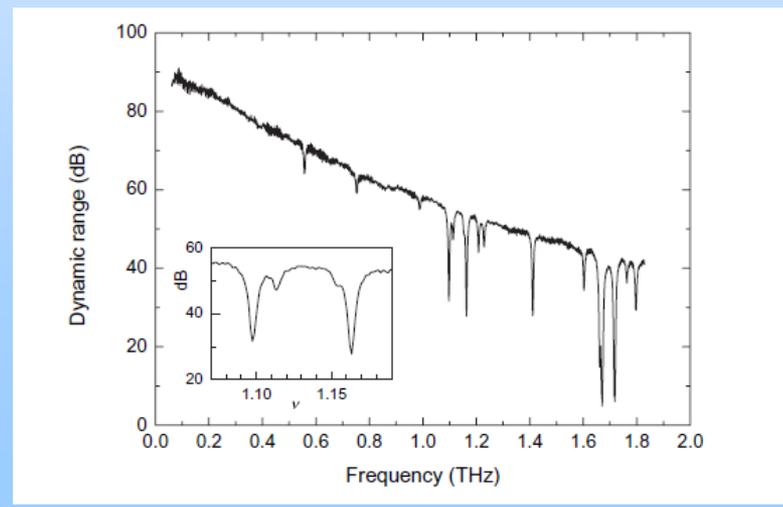
**Low efficiency !  
Requires further  
improvements**

# 2-laser diodes CW THz systems

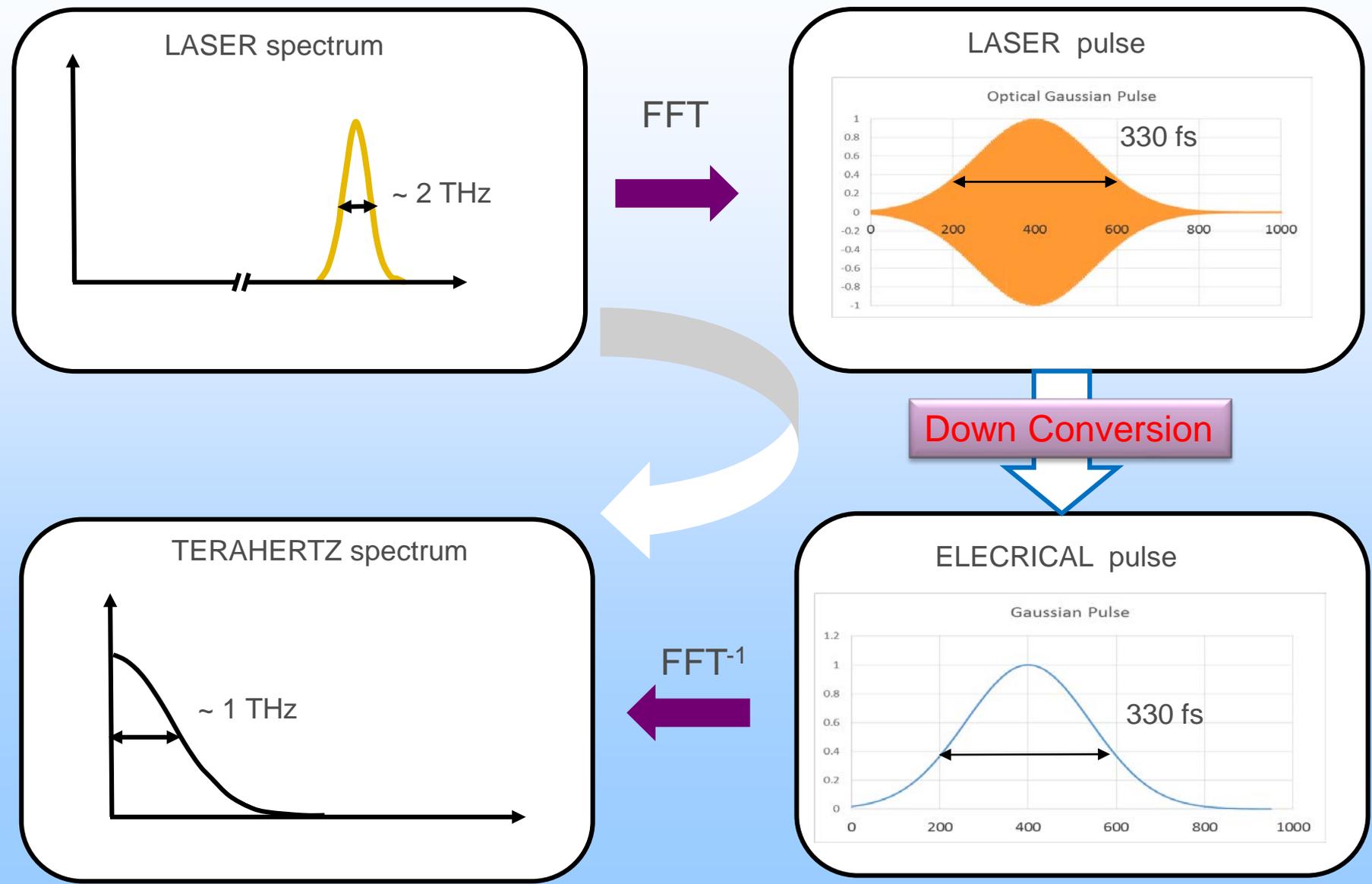
## Commercial equipment (Germany)



Wavelength range*	853 + 855 nm	1546 + 1550 nm
Lasers	2x DL DFB	TeraBeam 1550
Laser power (fiber output)	2 x 50 mW	2 x 30 mW
Scan range per diode	± 1.3 nm	± 2.2 nm
Frequency accuracy	2 GHz absolute , 10 MHz relative	
THz scan range	Typ. 0 – 1800 GHz	Typ. 0 – 1200 GHz
Optical isolation	60 dB per laser	80 dB per laser



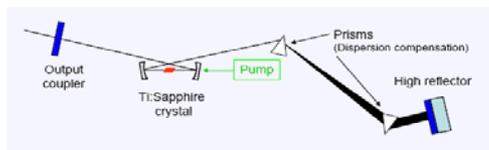
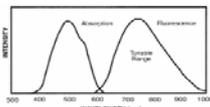
# From Optics down to THz: case of pulsed regime



# Femtosecond lasers for THz pulse generation

## Kerr lens modelocked Ti:Sa

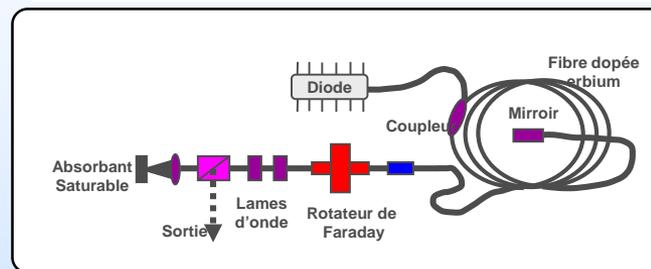
- Ti:sapphire has large bandwidth
- Supports shortest pulses
- Simple (amazingly)



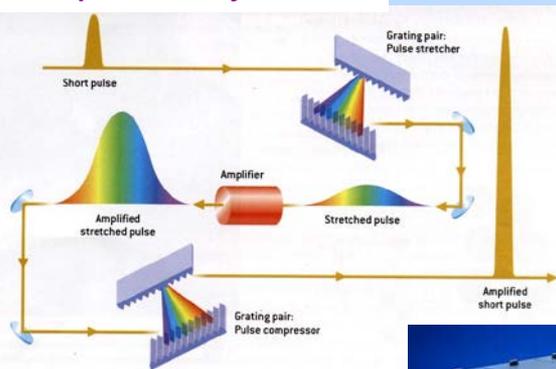
M.T. Asaki, et al, Opt. Lett. 18, 977 (1993)



## Erbium doped fiber modelocked laser



## Amplified Systems



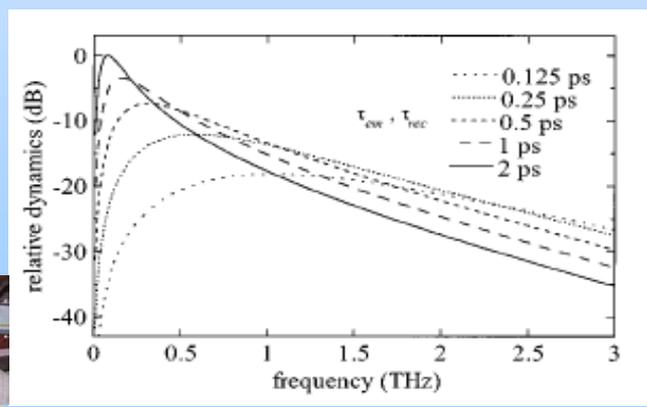
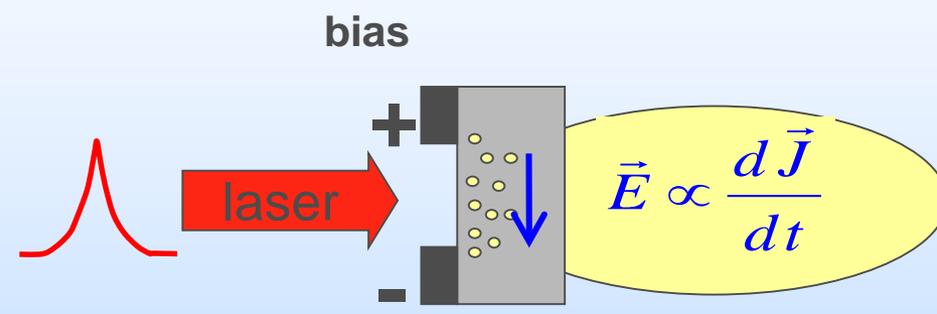
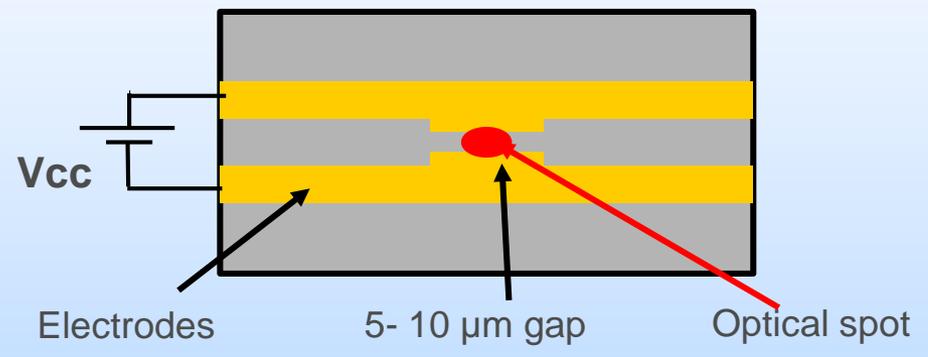
## Plenty of Commercial lasers available

- from 800 to 2200 nm wavelength
- from 12 to 250 fs
- from 1 kHz to 1 GHz rep. Rate
- from nJ to mJ per pulse
- from 20 k€ to 300 k€

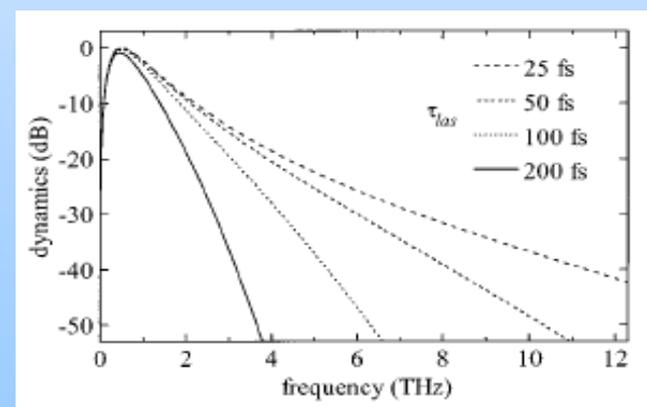
# Pulsed THz emission with a dipole antenna



## Typical photoconductive antenna



Spectre calculé pour différents temps de vie des porteurs ( $\Delta t$  laser = 80fs)

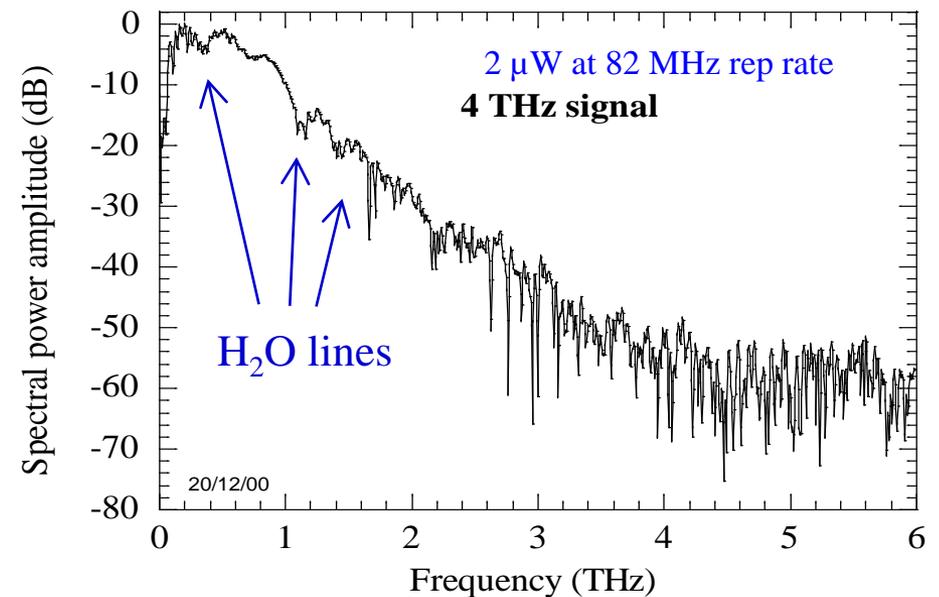
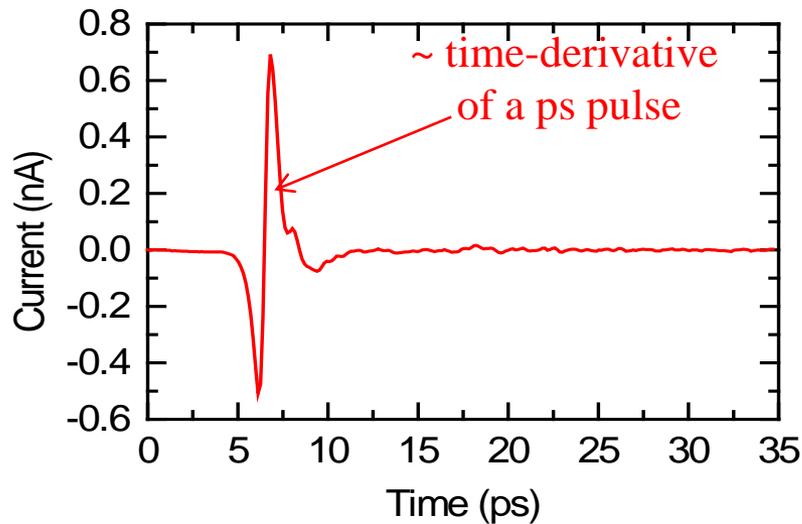


Spectre calculé pour différents Durée d'impulsion laser ( $\tau$  porteurs = 300fs)



# Typical THz signal radiated by a photoswitch

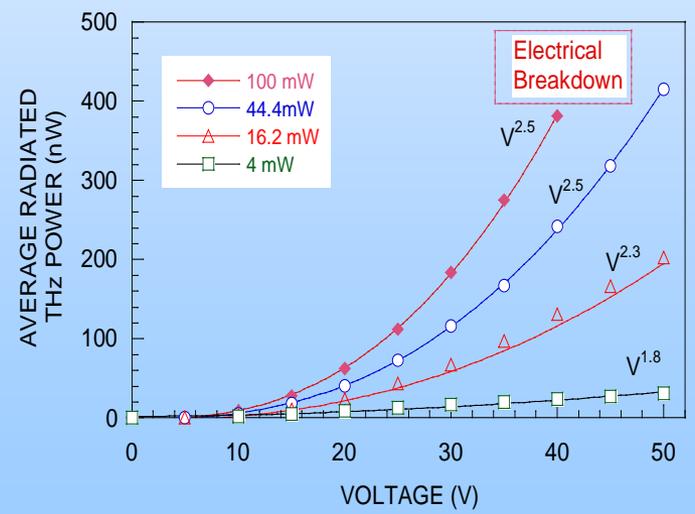
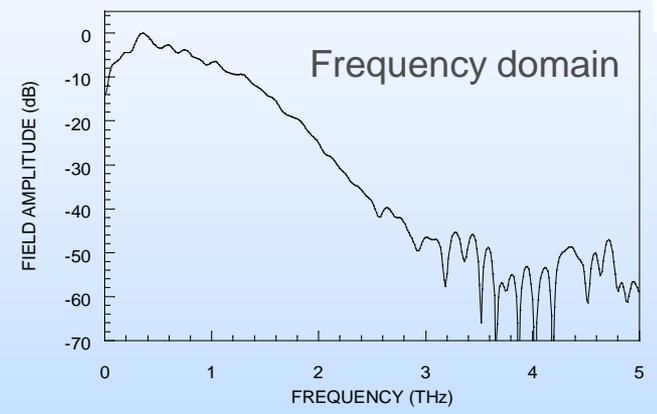
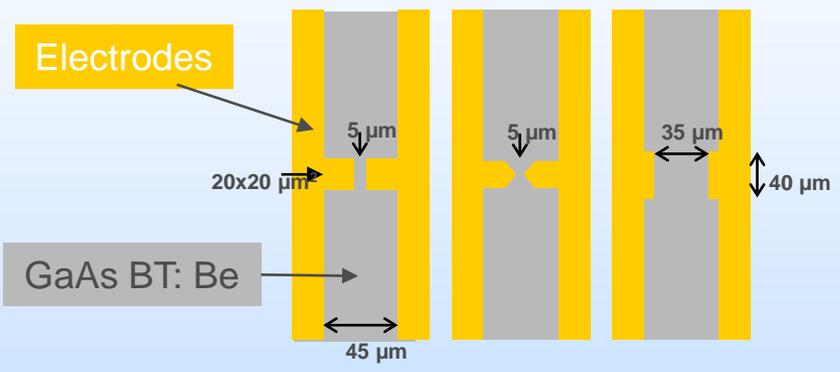
- Photoconductive emission using a femtosecond Ti:Sa Oscillator (100 MHz, 500 mW)



# Pulsed THz emission with dipole antenna PSW



- Photoconductive emission using optimized dipole antenna



$P(\text{THz})$  varies with  $V_{\text{bias}}^2$  and  $P_{\text{opt}}^2$



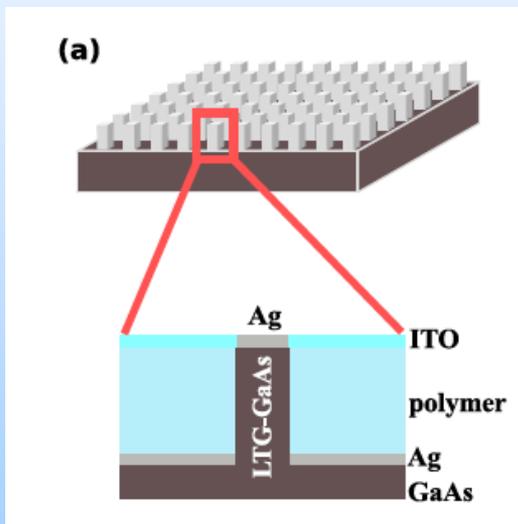
$P_{\text{THz}} = 10 \mu\text{W}$  broadband  
Cost = 1500 €

# Improved 3D device based on nano-photonics and plasmonic effects

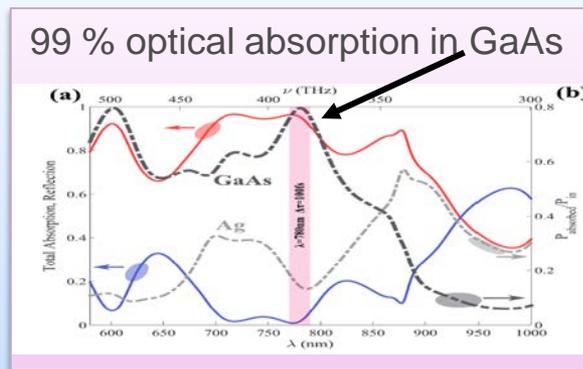
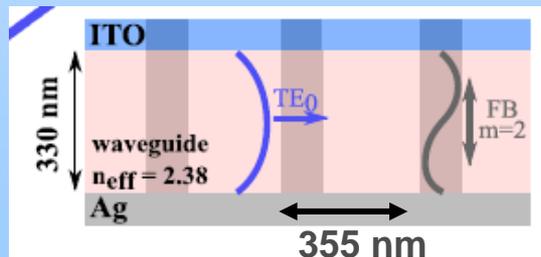


- Our goal is to have very efficient component to generate ps pulses with very low amount of optical power

## Array of GaAs nano-pillars

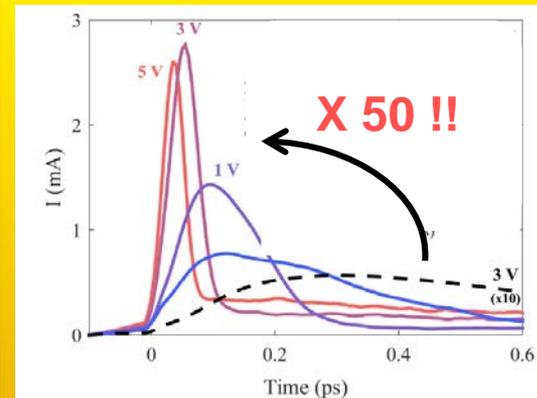


Waveguide resonance  
+  
Fabry- Perot resonance  
+  
Plasmon excitation

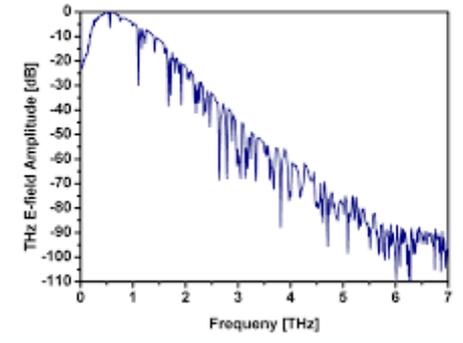


Simulation results

Pulsed current 50 times larger than in classic device



# THz Time Domain Spectroscopy Systems based on pulsed THz generation in photoswitches



*Prog. Quant. Electr.*, Vol. 4, pp. 207-232. Pergamon Press, 1976. Printed in Great Britain

## FAR-INFRARED GENERATION BY OPTICAL MIXING

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The motivation for studying far-infrared generation by this method is twofold. First, the far-infrared generation is closely related to other nonlinear optical processes such as the electro-optical effect, sum-frequency generation, etc. By studying the various nonlinear optical processes, we can have a better understanding of not only the nonlinear optical properties of matter, but also optical wave propagation in a nonlinear medium. Secondly, we hope to find a new far-infrared source which is superior to those presently available. This second aspect is clearly of practical importance; let us therefore elaborate a little on it.

# Non-linear Optics : second order effects

$$\frac{\partial^2 \vec{E}}{\partial z^2} - \frac{1}{c^2} \frac{\partial^2 \vec{E}}{\partial t^2} = \mu_0 \frac{\partial^2 \vec{P}}{\partial t^2} \quad \text{With}$$

$$\vec{P} = \varepsilon_0 \chi^{(1)} \vec{E} + \varepsilon_0 \left[ \chi^{(2)} \vec{E}^2 + \dots \right]$$

$P_{NL}$  generally very weak...

- Consider the interaction between 2 waves at  $\omega_1$  et  $\omega_2$  in a non-linear  $\chi^{(2)}$  media

$$E(t) = \frac{1}{2} \{ A_1 \exp(i\omega_1 t - ik_1 z) + cc \} + \frac{1}{2} \{ A_2 \exp(i\omega_2 t - ik_2 z) + cc \}$$

The non-linear polarization is proportionnal to :

$$E(t)^2 \propto A_1^2 \exp(2i\omega_1 t - 2ik_1 z) + cc$$

2nd-harmonic gen

$$+ A_2^2 \exp(2i\omega_2 t - 2ik_2 z) + cc$$

2nd-harmonic gen

$$+ 2A_1 A_2 \exp[i(\omega_1 + \omega_2)t - i(k_1 + k_2)t] + cc$$

Sum-freq gen

$$+ 2A_1 A_2^* \exp[i(\omega_1 - \omega_2)t - i(k_1 - k_2)t] + cc$$

Difference-freq. generation

$$+ 2|A_1|^2 + 2|A_2|^2$$

Rectification

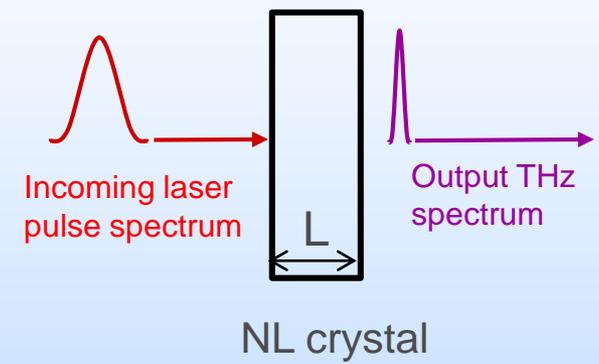
# THz Generation by optical rectification

NL Helmutz equation

$$\frac{\partial^2 E(\omega_{THz}, z)}{\partial z^2} + k_{THz}^2 E(\omega_{THz}, z) = -\frac{\omega_{THz}^2}{\epsilon_0 c^2} P_{NL}(\omega_{THz}, z)$$

Source term at  $\omega_{THz}$

$$P_{NL}(\omega_{THz}, z) = \epsilon_0 \cdot \chi^{(2)}(\omega_{THz}) \cdot E_{laser}^2 \cdot S(\omega_{THz}) \cdot \exp(i \frac{\omega_{THz}}{V_g} z)$$



Generated Field at  $\omega_{THz}$

$$E_{THz}(\omega_{THz}, L) = i \frac{\omega_{THz}^2}{c^2} \cdot \chi^{(2)}(\omega_{THz}) \cdot E_{laser}^2 \cdot S(\omega_{THz}) \cdot L \exp\left(i \left(k_{THz} + \frac{\omega_{THz}}{V_g}\right) \frac{L}{2}\right) \left[ \frac{\sin(\Delta k L / 2)}{\Delta k} \right]$$

- Nonlinear coeff of the crystal
- Laser peak amplitude
- Spectral density depends on laser pulse duration

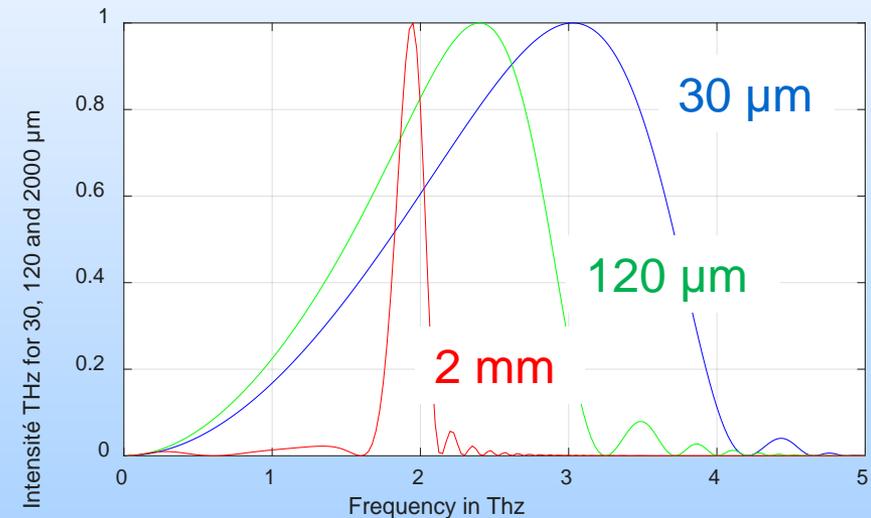
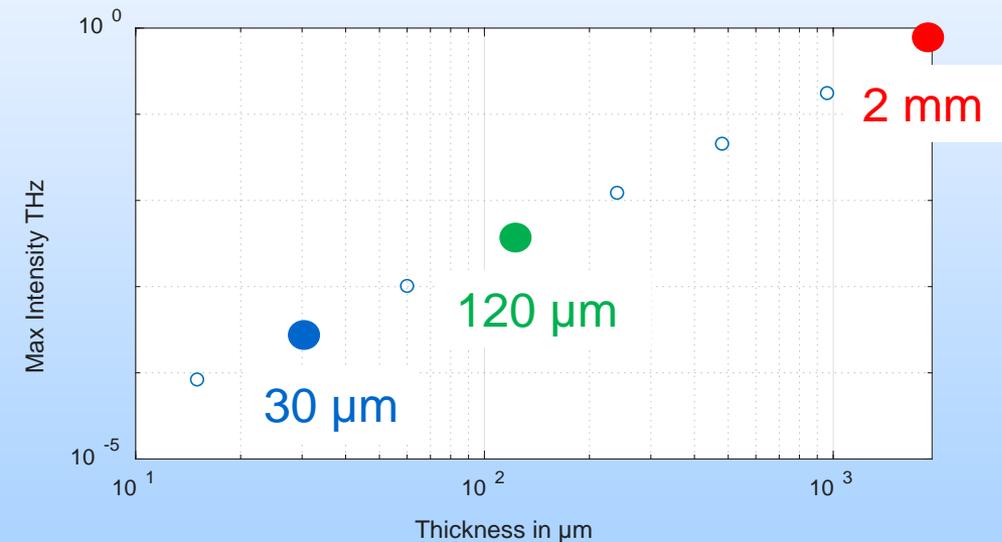
$\Delta k \equiv \omega_{THz} \left( \frac{n_{THz}}{c} - \frac{1}{V_g} \right)$

**Phase mismatch** due to velocity mismatch:

- the NL terms propagates at the IR group velocity  $V_g$
- The THz wave propagates at the THz phase velocity...

# THz Generation by optical rectification

$$I_{THz}(\omega_{THz}, L) \propto \frac{\omega_{THz}^4}{c^4} \left[ \chi^{(2)}(\omega_{THz}) \cdot I_{laser} \cdot S(\omega_{THz}) \right]^2 \cdot L^2 \left[ \frac{\sin(\Delta k L / 2)}{\Delta k} \right]^2$$



- Thick Crystal = High power
- Thin Crystal = large THz spectrum

# Figure of Merit of usual non-linear crystals for DFG

crystal	EO coefficient	refractive index	DC dielectric constant	figure of merit (rectification)	GVD	EOS $V_\pi$	phonon $f_{TO}$
	(pm/V)			(pm/V)	(ps/mm)	(kV)	(THz)
ZnTe	$r_{41}= 4,04$	$n=2,853$	$\epsilon=10,1$	$\sim 45$	<b>1,1</b>	6,75	5,3
LiTaO <sub>3</sub>	$r_{33}= 30,5$ $r_{13}= 8,4$	$n_o=2,176$ $n_e=2,180$	$\epsilon_{1,2}=41$ $\epsilon_{1,2}=43$	$\leq 85$	14,1	2,01 7,27	6,23
LiNbO <sub>3</sub>	$r_{33}= 30,9$ $r_{51}= 32,6$	$n_o=2,286$ $n_e=2,200$	$\epsilon_{1,2}=43$ $\epsilon_3=28$	$\leq 110$	14,2	1,71 1,82	4,5
KTP	$r_{33}= 36,3$ $r_{23}= 15,7$	$n_e=1,866$	$\epsilon_{1,2}=11$ $\epsilon_3=15$	$\leq 109$	5,4	2,68	
DAST	$r_{11}= 77$	$n_o=2,46$ $n_e=1,70$	8,0 2,9	$\leq 600$	<b>1,22</b>	0,71 2,16	<b>2.28 i=1</b> <b>1.13 i=2</b> <b>1.50 i=3</b>

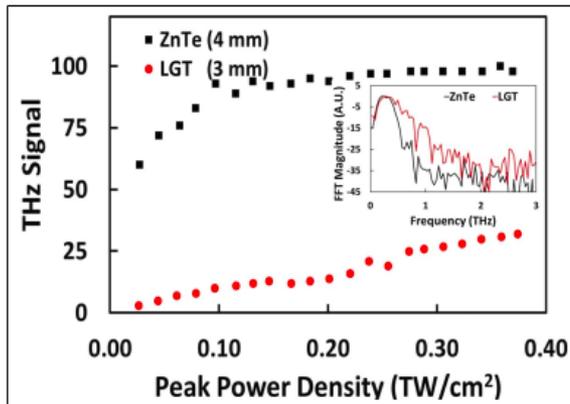
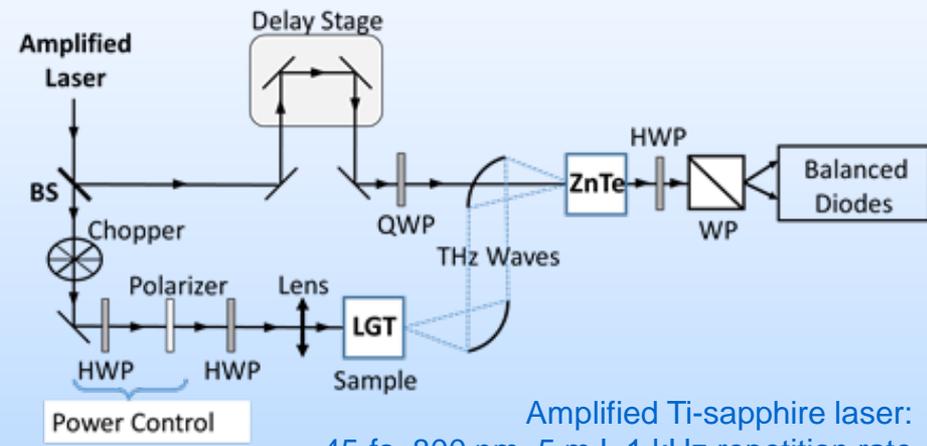
Choice of the crystal depends on the application... and on the source

# Terahertz generation in a langatate crystal by optical rectification



Langatate crystal  
 $\text{La}_3\text{Ga}_{5.5}\text{Ta}_{0.5}\text{O}_{14}$

- Piezoelectric properties
- No phase change up to its melting point (1450 ° C)
- Piezoelectric constant ( $d_{11}$ ) stable up to 600°C
- Damage threshold 6 times higher than  $\text{LiNbO}_3$

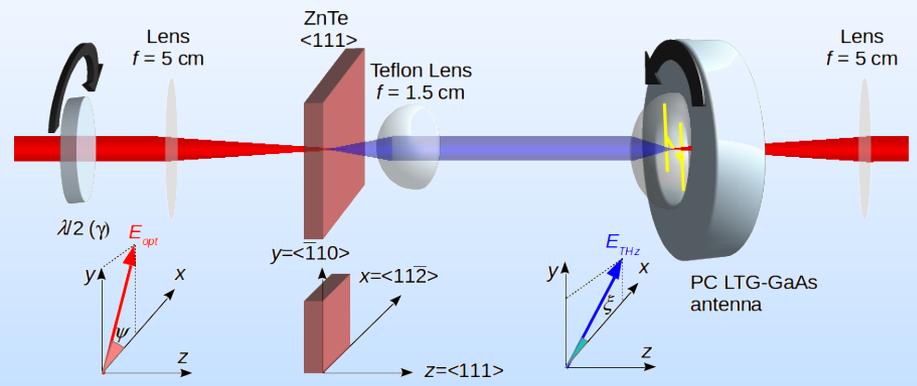


- ZnTe crystal generates more THz signal than LGT, it starts to saturate over 0.1 TW/cm<sup>2</sup>.
- However, LGT crystal presents a good linearity up to 0.37 TW/cm<sup>2</sup>

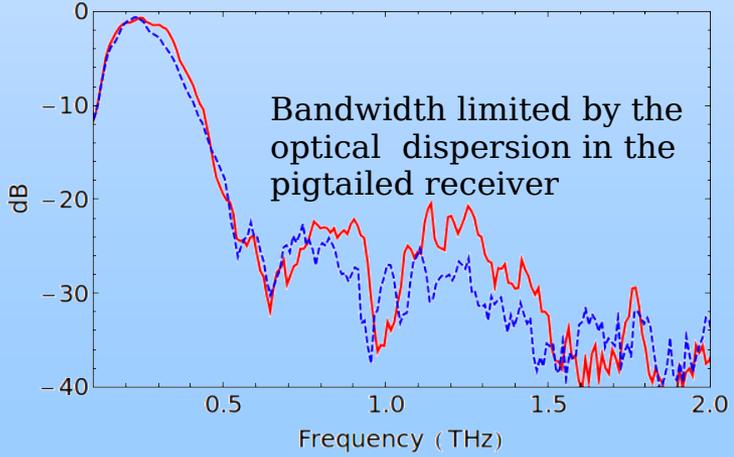


# Control of the THz polarization state by optical rectification within a cubic crystal

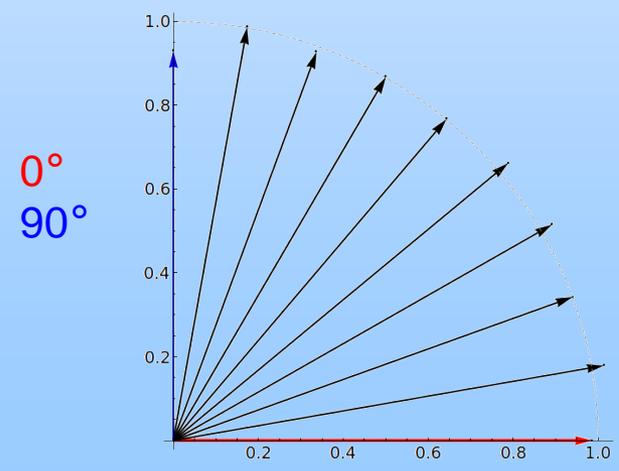
- OR is linked to the group symetry of the crystals : use of a cubic crystal to control THz polarization by rotating the IR pulses polarization



THz spectrum

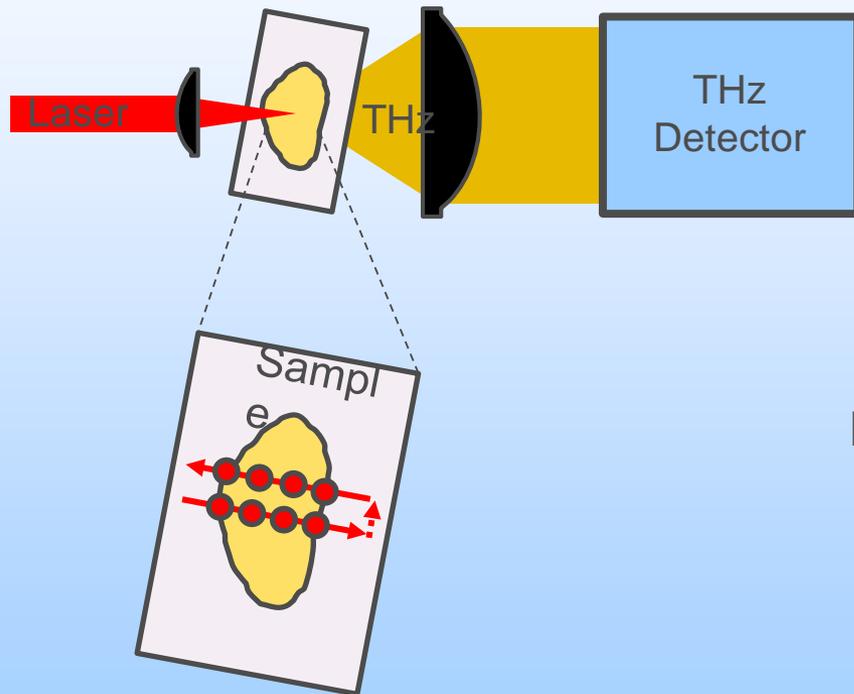


THz polarization state



# Optical rectification TeraHertz Imaging

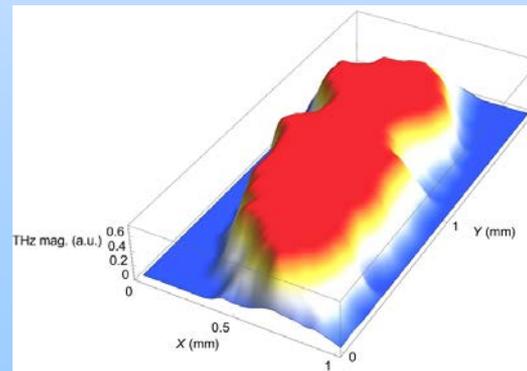
Idea : Probing and imaging the structure of a material by probing its NL « local » properties through THz generation



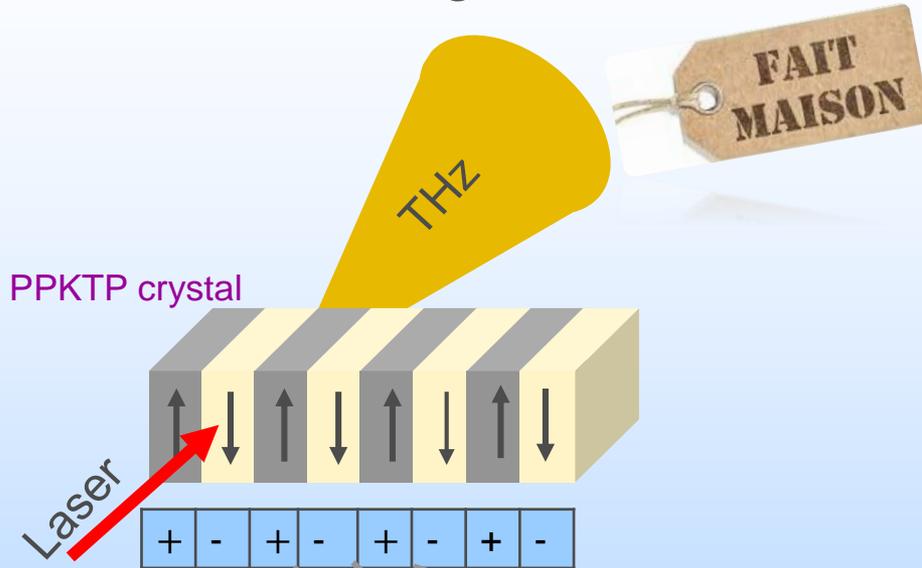
→ Imaging point by point by moving the sample

→ Resolution depends on laser spot size not on THz wavelength

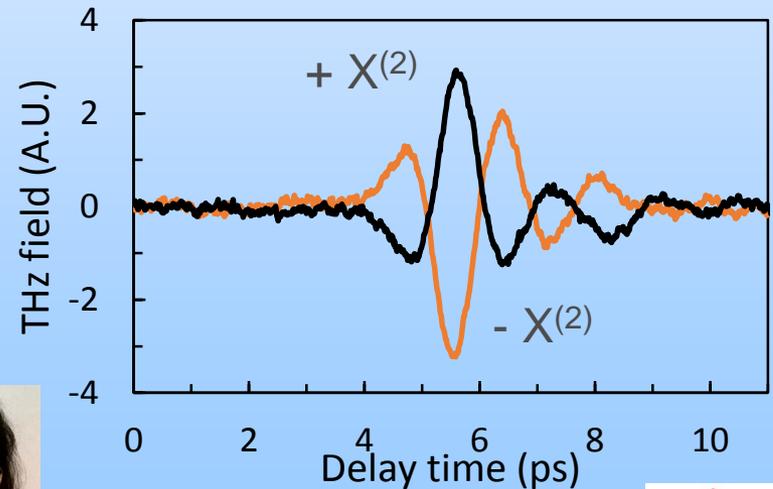
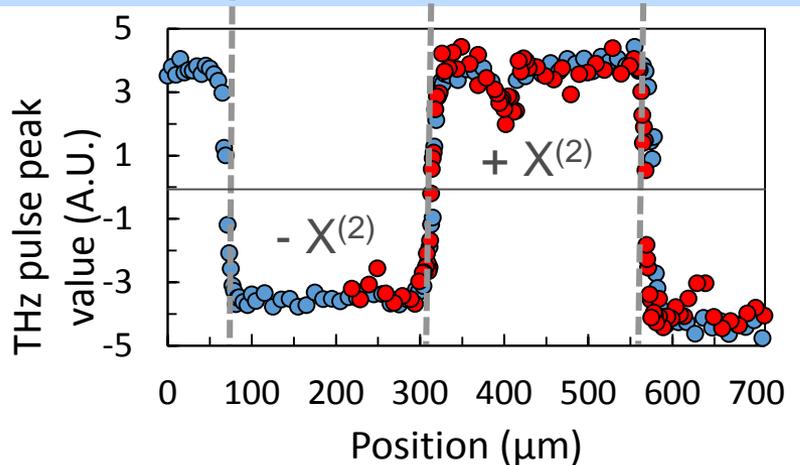
Imaging of a sugar grain



# Optical rectification TeraHertz Imaging in PPKTP crystals



- Imaging point by point by moving the sample
- Resolution depends on laser spot size not on THz wavelength
- Imaging PPKTP crystal: Generated THz waves should be inverted as the crystal orientation is flipped !



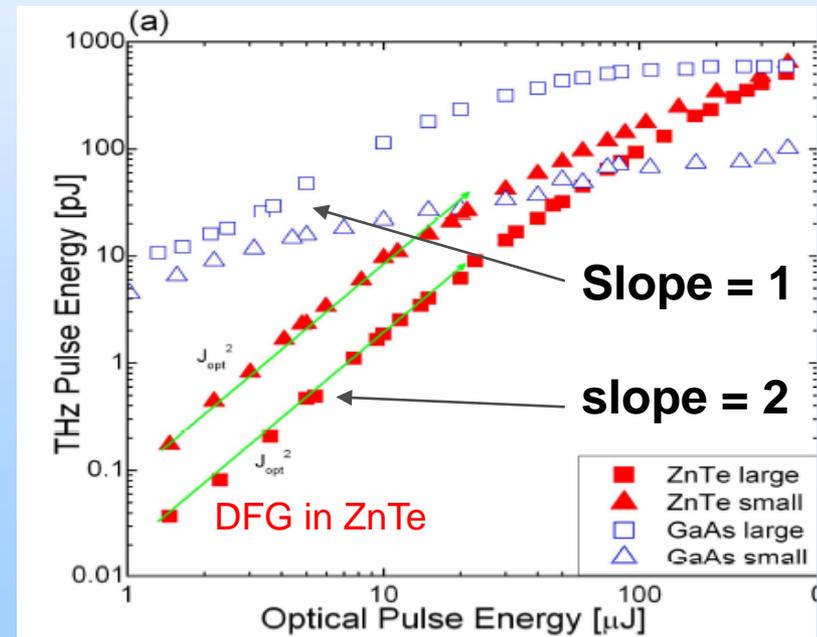
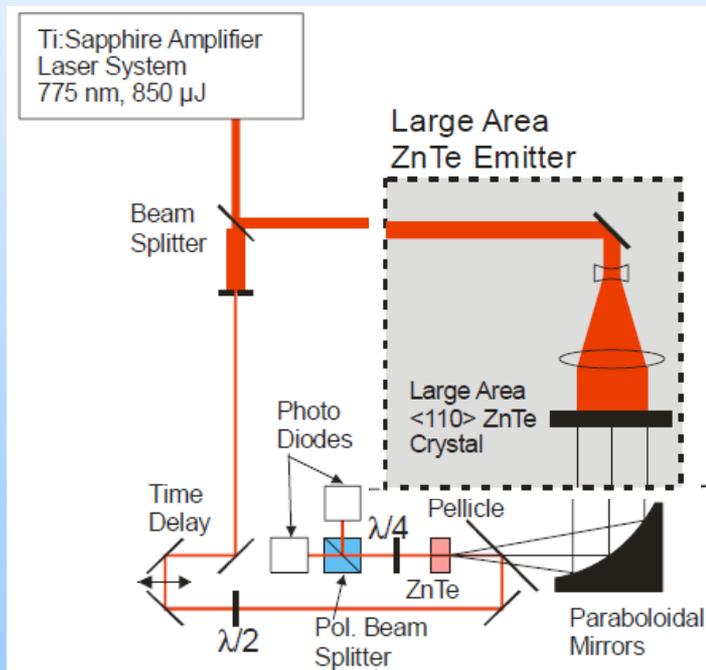
Gizem Soylu's work



# Towards high THz power generation using amplified pulsed lasers

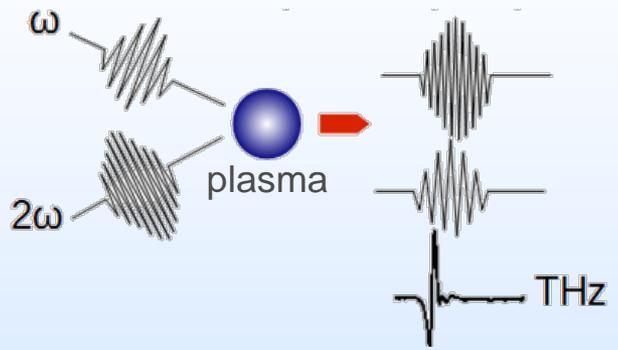
- Use of large area nonlinear crystal (ZnTe)

850  $\mu\text{J}/\text{pulse}$  (150 fs)  
Rep. Rate = 1 kHz

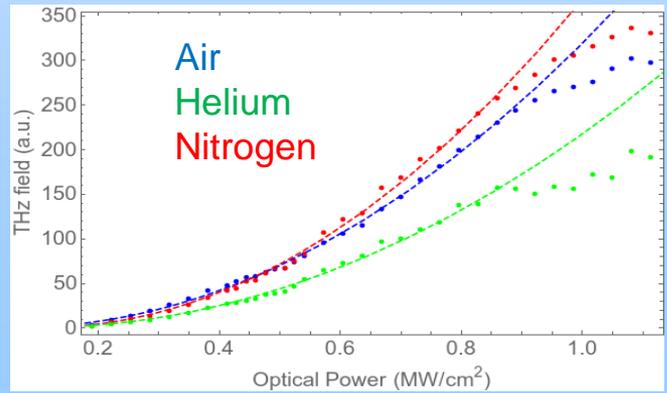
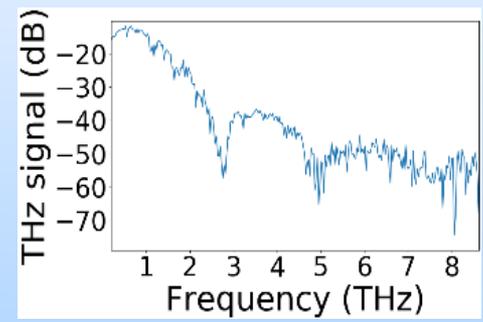
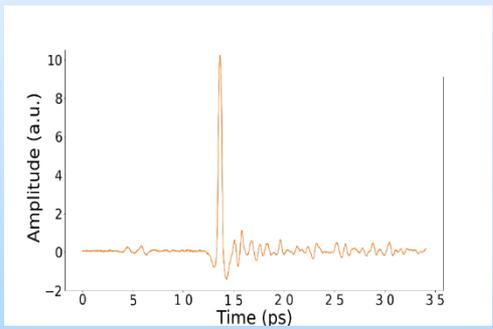
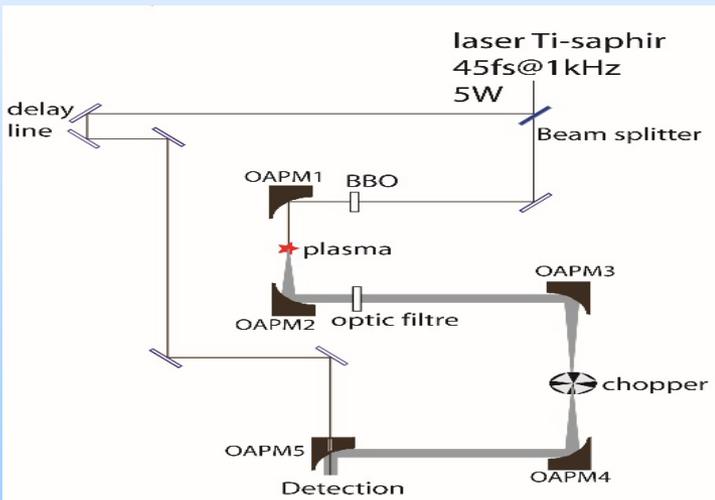


Max THz field = 10 kV/cm

# THz generation in Plasma



- Photo-generated plasma by femtosecond optical breakdown in air
- Acceleration of ions and e- by charge repulsion and ponderomotive force
- Radiation of electromagnetic signal by the accelerated charges
- $\omega$  and  $2\omega$  light beams induce a dipole-like symmetry breaking
- Intense THz peak power (THz fields over MV/cm)



# Spectroscopie THz ultra-large bande à l'Université Technologique du Danemark (P. Jepsen)

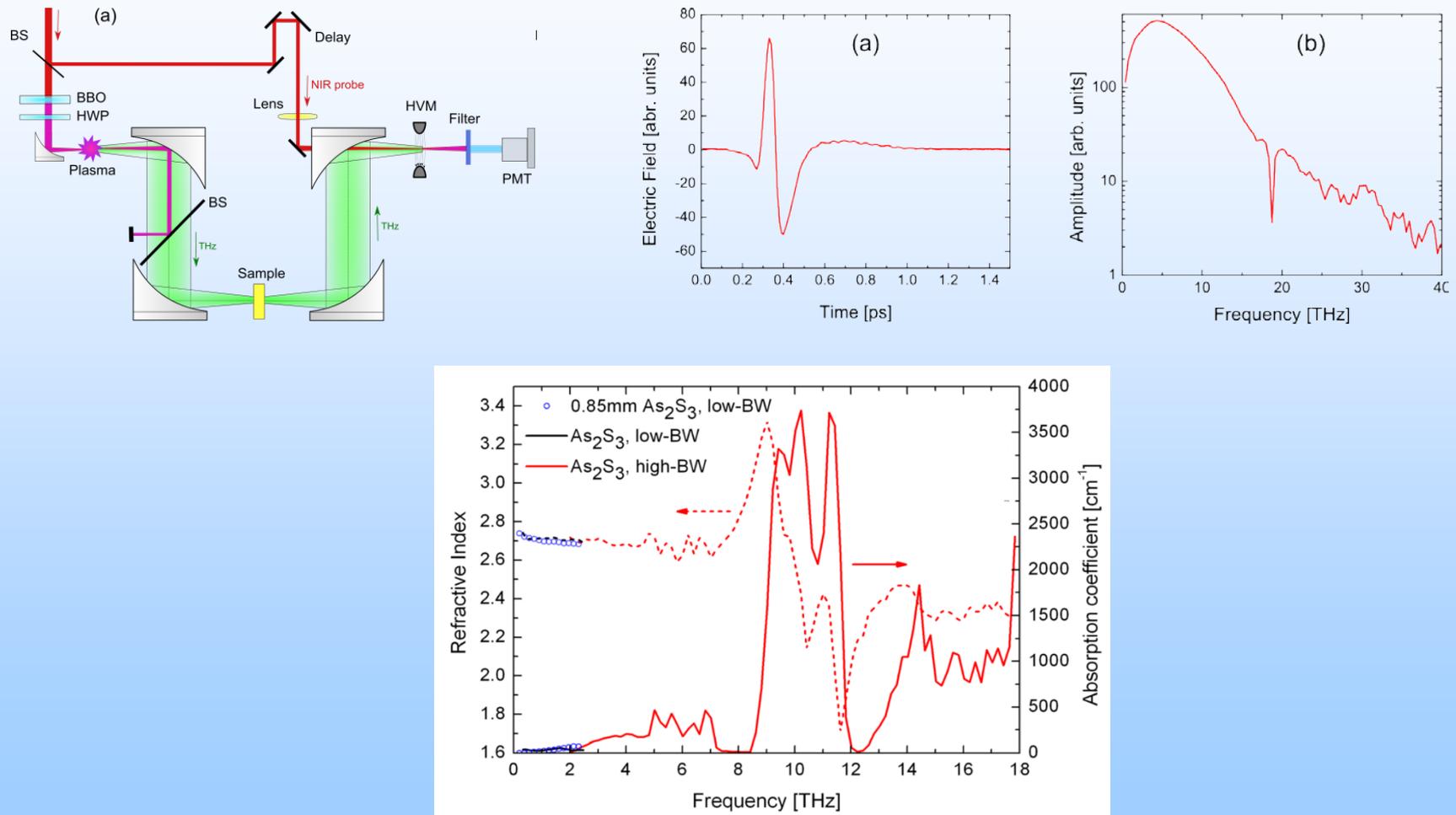


Figure 3: Refractive index (dashed line) and absorption coefficient (solid line) of As<sub>2</sub>S<sub>3</sub>. The high bandwidth measurements are performed by THz-ABCD system (red) for 13.6  $\mu\text{m}$  thick sample. For comparison the spectroscopy results by photoconductive antenna-based THz-TDS system on thin (black) samples and on a 0.85 mm thick (blue circles) sample

# THz sources: who is the winner ?

## CW sources

**below 600 GHz:** **Transistors based oscillators** are Ultra-compact, Powerful, Versatile, CMOS Integrated, Low-Cost (?)

**above 4 THz:** **Quantum Cascade Lasers** are working at « Room Temperature » (quasi), Ultra-compact, Powerful, Efficient

**fr. 0.6 to 4 THz:** **Down Conversion of Photonic Sources** offers large panel of possibilities such as tunability, narrow linewidth, CW or pulsed regime etc...

## Broadband sources

**incoherent:** **Blackbody radiation** is popular, low cost, reliable

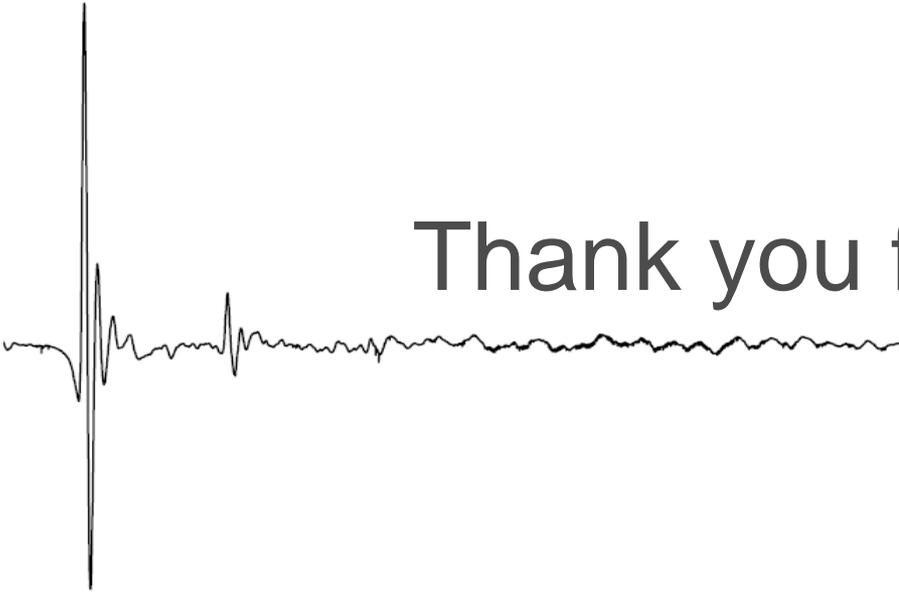
**coherent:** **Down conversion of fs pulses** offers ultrastable THz pulses, large measurements dynamics, versatile, potentially High Peak power

# CONCLUSION

source	gamme spectrale (THz)	puissance	avantages	inconvénients
corps noir	toute la gamme	pW à 0,1 THz $\mu$ W à 10 THz	simplicité large bande	puissance incohérent
Gunn	0,1 → 1	100 mW CW 1 mW CW	compact	fréquence limitée
Impatt	→ 0,3	10 mW	compact	fréquence limitée
Tunett RTD	→ 0,4	10 $\mu$ W	compact	puissance fréquence limitée
Smith-Purcell	toute la gamme	100 nW	accordable	gros appareil
FEL	toute la gamme	très puissants → 100 W CW	puissance spectre	grands instruments
BWO	→ 0,2	10 $\mu$ W	compact accordable	bruyant fréquence limitée
lasers moléculaires	lignes spectrales	ex : CH <sub>3</sub> OH 100 mW à 2,52 THz	pureté spectrale	stabilité, volumineux
lasers QCL	1,9 ←	10 mW	compact, rendement	cryogénie puissance
optoélectronique impulsif	0,1 → 60	$\mu$ W	spectre cohérent, aspect temporel	puissance limitée, résolution spectrale
CW battement optique	→ 3	$\mu$ W	compact, pureté spectrale	puissance faible

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- Antoine Kervorkian and Grégoire Souhaité from Teem Photonics



Thank you for your attention,